

### 16-BIT SINGLE-CHIP MICROCONTROLLERS

#### DESCRIPTION

The  $\mu$ PD78F4216A/78F4218A and 78F4216AY/78F4218AY are products of  $\mu$ PD784216A/784218A, 784216AY/784218AY Subseries in the 78K/IV Series.

The  $\mu$ PD78F4216A/78F4218A have flash memory in place of the internal ROM of the  $\mu$ PD784216A/784218A. The incorporation of flash memory allows a program to be written or erased while mounted on the target board.

The  $\mu$ PD78F4216AY/78F4218AY are based on the  $\mu$ PD78F4216A/78F4218A Subseries with the addition of a multimaster-supporting I<sup>2</sup>C bus interface.

Detailed function descriptions are provided in the following user's manuals. Be sure to read them before designing.

$\mu$ PD784216A, 784216AY Subseries User's Manual Hardware: U13570E

$\mu$ PD784218A, 784218AY Subseries User's Manual Hardware: U12970E

78K/IV Series User's Manual Instructions: U10905E

#### FEATURES

- Pin compatible with the mask ROM products
- Flash memory: 128 KB ( $\mu$ PD78F4216A/78F4216AY)  
256 KB ( $\mu$ PD78F4218A/78F4218AY)
- Internal RAM: 8,192 bytes ( $\mu$ PD78F4216A/78F4216AY)  
12,800 bytes ( $\mu$ PD78F4218A/78F4218AY)
- Supply voltage:  $V_{DD} = 1.9$  to 5.5 V

#### APPLICATIONS

Cellular phones, PHS, cordless telephones, CD-ROM, AV equipment

Unless otherwise specified, references in this document to the  $\mu$ PD78F4218AY refer to the  $\mu$ PD78F4216A, 78F4218A, 78F4216AY, and 78F4218AY.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.  
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

## ORDERING INFORMATION

Part Number	Package	Internal ROM (Bytes)	Internal RAM (Bytes)
$\mu$ PD78F4216AGC-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	128 K	8,192
$\mu$ PD78F4216AGF-3BA	100-pin plastic QFP (14 × 20)	128 K	8,192
$\mu$ PD78F4218AGC-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	256 K	12,800
$\mu$ PD78F4218AGF-3BA	100-pin plastic QFP (14 × 20)	256 K	12,800
$\mu$ PD78F4216AYGC-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	128 K	8,192
$\mu$ PD78F4216AYGF-3BA	100-pin plastic QFP (14 × 20)	128 K	8,192
$\mu$ PD78F4218AYGC-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	256 K	12,800
$\mu$ PD78F4218AYGF-3BA	100-pin plastic QFP (14 × 20)	256 K	12,800

78K/IV SERIES LINEUP

: Products in mass-production

: Products under development

**Standard models**

μPD784026

Enhanced A/D converter, 16-bit timer, and power management

Supports I<sup>2</sup>C bus

μPD784038Y

μPD784038

Enhanced internal memory capacity  
Pin-compatible with the μPD784026

Supports multimaster I<sup>2</sup>C bus

μPD784225Y

μPD784225

80-pin, ROM correction added

Supports multimaster I<sup>2</sup>C bus

μPD784216AY

μPD784216A

100-pin, enhanced I/O and internal memory capacity

Supports multimaster I<sup>2</sup>C bus

μPD784218AY

μPD784218A

Enhanced internal memory capacity, ROM correction added

μPD784054

μPD784046

On-chip 10-bit A/D converter

**ASSP models**

μPD784956A

For DC inverter control

μPD784908

On-chip IEBus™ controller

μPD784938A

Enhanced functions of the μPD784908, enhanced internal memory capacity, ROM correction added.

μPD784967

Enhanced functions of the μPD784938A, enhanced I/O and internal memory capacity.

Supports multimaster I<sup>2</sup>C bus

μPD784928Y

μPD784928

Enhanced functions of the μPD784915

μPD784915

Software servo control  
On-chip analog circuit for VCRs  
Enhanced timer

μPD784976

On-chip VFD controller/driver

OVERVIEW OF FUNCTIONS (1/2)

Part Number		μPD78F4216A, μPD78F4216AY	μPD78F4218A, μPD78F4218AY
Item			
Number of basic instructions (mnemonics)		113	
General-purpose registers		8 bits × 16 registers × 8 banks, or 16 bits × 8 registers × 8 banks (memory mapping)	
Minimum instruction execution time		<ul style="list-style-type: none"> <li>• 160 ns/320 ns/640 ns/1,280 ns/2,560 ns (@f<sub>xx</sub> = 12.5 MHz operation with main system clock)</li> <li>• 61 μs (@f<sub>XT</sub> = 32.768 kHz operation with subsystem clock)</li> </ul>	
Internal memory	Flash memory	128 KB	256 KB
	RAM	8,192 bytes	12,800 bytes
Memory space		1 MB with program and data spaces combined	
I/O ports	Total	86	
	CMOS input	8	
	CMOS I/O	72	
	N-ch open-drain I/O	6	
Pins with additional functions <sup>Note 1</sup>	Pins with pull-up resistor	70	
	LED direct drive output	22	
	Middle-voltage pin	6	
Real-time output port		4 bits × 2 or 8 bits × 1	
Timer/event counter		Timer/event counter: (16-bit)	Timer counter × 1 Capture/compare register × 2 Pulse output • PPG output • Square wave output • One-shot pulse output
		Timer/event counter 1: (8-bit)	Timer counter × 1 Compare register × 1 Pulse output • PWM output • Square wave output
		Timer/event counter 2: (8-bit)	Timer counter × 1 Compare register × 1 Pulse output • PWM output • Square wave output
		Timer/event counter 5: (8-bit)	Timer counter × 1 Compare register × 1 Pulse output • PWM output • Square wave output
		Timer/event counter 6: (8-bit)	Timer counter × 1 Compare register × 1 Pulse output • PWM output • Square wave output
		Timer/event counter 7: (8-bit)	Timer counter × 1 Compare register × 1 Pulse output • PWM output • Square wave output
		Timer/event counter 8: (8-bit)	Timer counter × 1 Compare register × 1 Pulse output • PWM output • Square wave output
		Serial interface	
A/D converter		8-bit resolution × 8 channels	
D/A converter		8-bit resolution × 2 channels	

**Notes** 1. Pins with additional functions are included with the I/O pins.

2. μPD78F4216AY, 78F4218AY only

OVERVIEW OF FUNCTIONS (2/2)

Item		Part Number	μPD78F4216A, μPD78F4216AY	μPD78F4218A, μPD78F4218AY
Clock output			Selectable from $f_{xx}$ , $f_{xx}/2$ , $f_{xx}/2^2$ , $f_{xx}/2^3$ , $f_{xx}/2^4$ , $f_{xx}/2^5$ , $f_{xx}/2^6$ , $f_{xx}/2^7$ , $f_{XT}$	
Buzzer output			Selectable from $f_{xx}/2^{10}$ , $f_{xx}/2^{11}$ , $f_{xx}/2^{12}$ , $f_{xx}/2^{13}$	
Watch timer			1 channel	
Watchdog timer			1 channel	
Standby			<ul style="list-style-type: none"> <li>• HALT/STOP/IDLE modes</li> <li>• In low power consumption mode (with subsystem clock): HALT/IDLE modes</li> </ul>	
Interrupt	Hardware sources		29 (internal: 20, external: 9)	
	Software sources		BRK instruction, BRKCS instruction, operand error	
	Non-maskable		Internal: 1, external: 1	
	Maskable		Internal: 19, external: 8	
			<ul style="list-style-type: none"> <li>• 4 programmable priority levels</li> <li>• 3 service modes: Vectored interrupt/macro service/context switching</li> </ul>	
Supply voltage			$V_{DD} = 1.9$ to $5.5$ V	
Package			100-pin plastic LQFP (fine pitch) ( $14 \times 14$ ) 100-pin plastic QFP ( $14 \times 20$ )	

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**1. DIFFERENCES AMONG MODELS IN μPD784216A/784216AY, 784218A/784218AY SUBSERIES**

The only difference among the μPD784214A, 784215A, 784216A, 784217A, and 784218A lies in the internal memory capacity.

The μPD784214AY, 784215AY, 784216AY, 784217AY, and 784218AY are models with the addition of an I<sup>2</sup>C bus control function.

The μPD78F4216A, 78F4216AY, 78F4218A, and 78F4218AY are provided with a 128 KB/256 KB flash memory instead of the mask ROM of the above models.

These differences are summarized in Table 1-1.

**Table 1-1. Differences Among Models in μPD784216A/784216AY, 784218A/784218AY Subseries**

Part Number	μPD784214A, μPD784214AY	μPD784215A, μPD784215AY	μPD784216A, μPD784216AY	μPD784217A, μPD784217AY	μPD784218A, μPD784218AY	μPD78F4216A, μPD78F4216AY	μPD78F4218A, μPD78F4218AY
Internal ROM	96 KB (Mask ROM)	128 KB (Mask ROM)		192 KB (Mask ROM)	256 KB (Mask ROM)	128 KB (Flash memory)	256 KB (Flash memory)
Internal RAM	3,584 bytes	5,120 bytes	8,192 bytes	12,800 bytes		8,192 bytes	12,800 bytes
Internal memory size switching register (IMS)	Not provided					Provided <sup>Note</sup>	
ROM correction	Not provided			Provided		Not provided	Provided
External access status function	Not provided			Provided		Not provided	Provided
Supply voltage	V <sub>DD</sub> = 1.8 to 5.5 V					V <sub>DD</sub> = 1.9 to 5.5 V	
Electrical specifications	Refer to the data sheet for each device.						
Recommended soldering conditions							
EXA pin	Not provided			Provided		Not provided	Provided
TEST pin	Provided					Not provided	
V <sub>PP</sub> pin	Not provided					Provided	

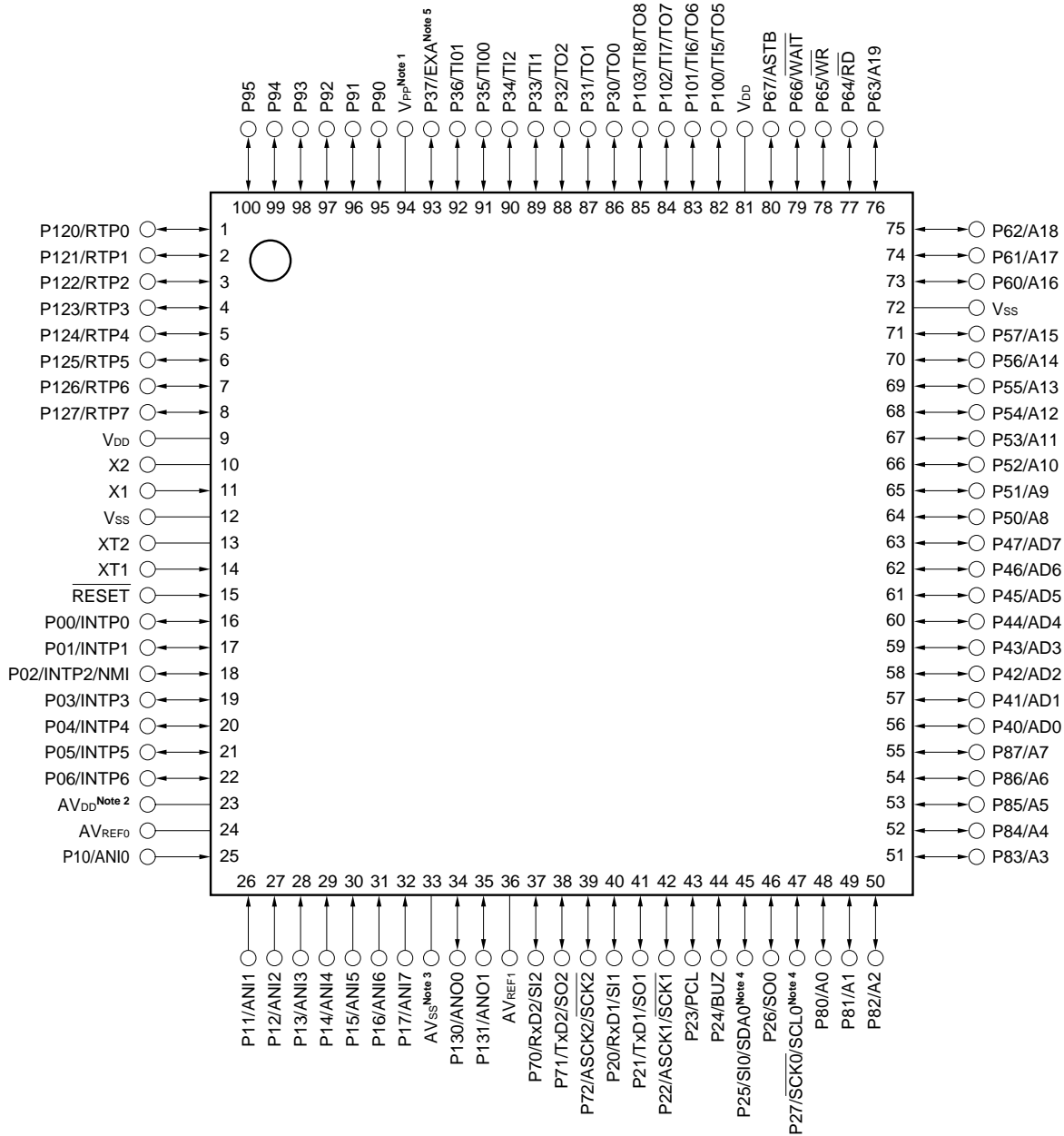
**Note** The internal flash memory capacity and internal RAM capacity can be changed using the internal memory size switching register (IMS).

**Caution** There are differences in noise immunity and noise radiation between the flash memory and mask ROM versions. When pre-producing an application set with the flash memory version and then mass-producing it with the mask ROM version, be sure to conduct sufficient evaluations on the commercial samples (not engineering samples) of the mask ROM version.

2. PIN CONFIGURATION (TOP VIEW)

- 100-pin plastic LQFP (fine pitch) (14 × 14)

μPD78F4216AGC-8EU, μPD78F4218AGC-8EU, μPD78F4216AYGC-8EU, μPD78F4218AYGC-8EU

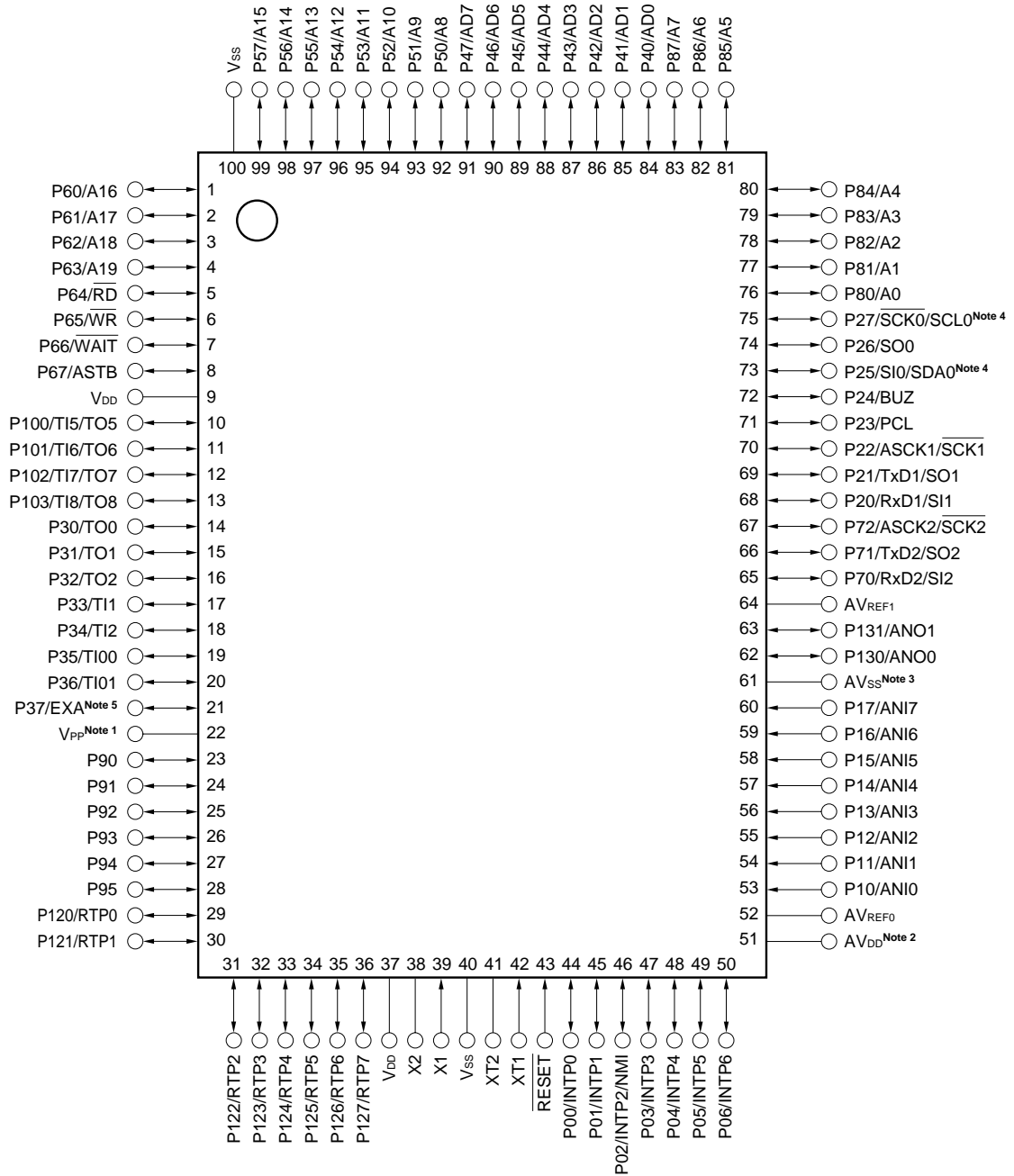


- Notes**
1. Connect the V<sub>PP</sub> pin to V<sub>SS</sub> directly or via a pull-down resistor in normal operation mode. Connect the V<sub>PP</sub> pin to V<sub>SS</sub> via a pull-down resistor in a system in which the on-chip flash memory is written while mounted on the target board. For the pull-down connection, it is recommended to use a resistor with a resistance ranging from 470 Ω to 10 kΩ.
  2. Connect the AV<sub>DD</sub> pin to V<sub>DD</sub>.
  3. Connect the AV<sub>SS</sub> pin to V<sub>SS</sub>.
  4. The SCL0 and SDA0 pins are available in the μPD78F4216AY, 78F4218AY only.
  5. The EXA pin is available in the μPD78F4218A, 78F4218AY only.



• 100-pin plastic QFP (14 × 20)

μPD78F4216AGF-3BA, μPD78F4218AGF-3BA, μPD78F4216AYGF-3BA, μPD78F4218AYGF-3BA



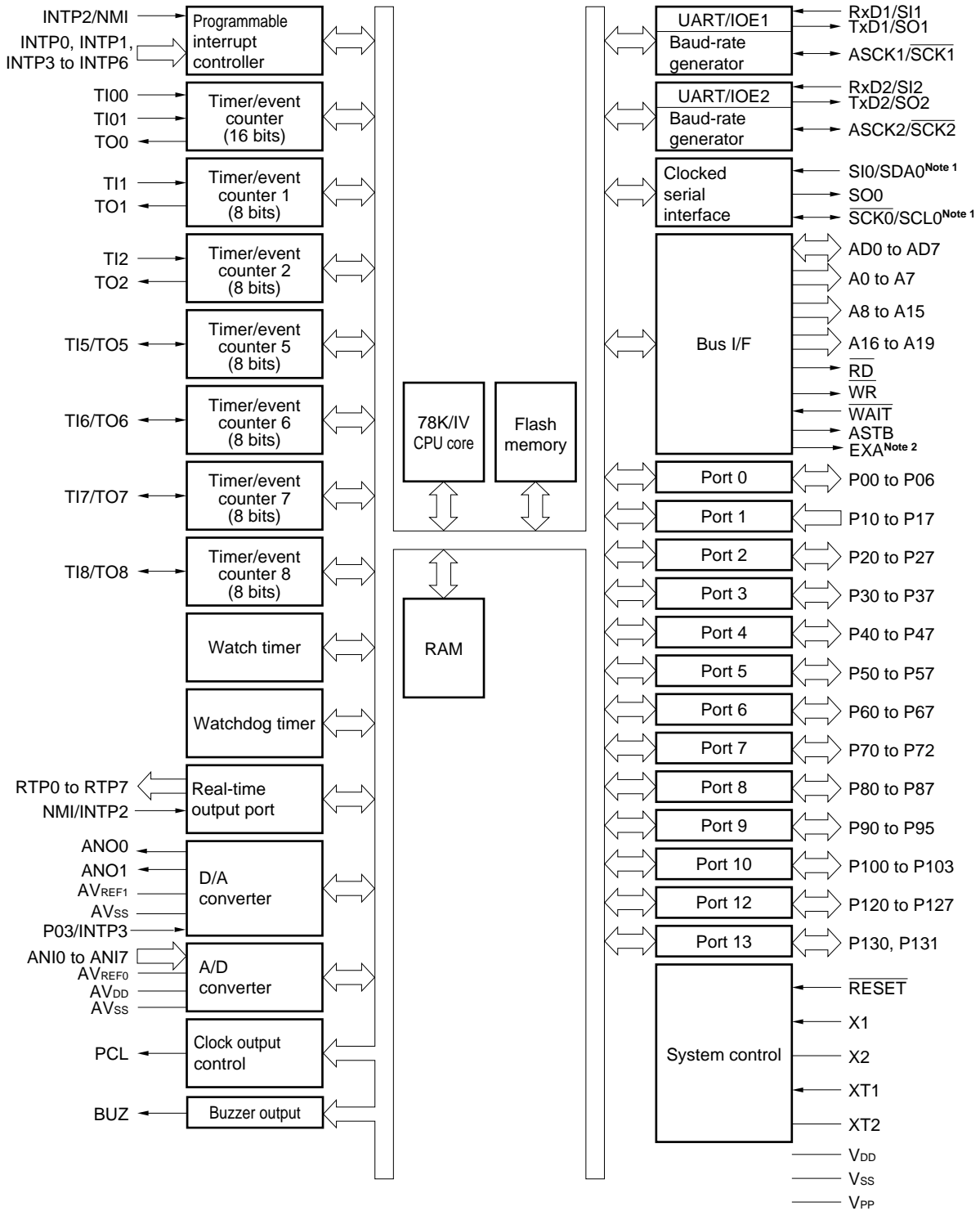
- Notes**
1. Connect the V<sub>PP</sub> pin to V<sub>SS</sub> directly or via a pull-down resistor in normal operation mode. Connect the V<sub>PP</sub> pin to V<sub>SS</sub> via a pull-down resistor in a system in which the on-chip flash memory is written while mounted on the target board. For the pull-down connection, it is recommended to use a resistor with a resistance ranging from 470 Ω to 10 kΩ.
  2. Connect the AV<sub>DD</sub> pin to V<sub>DD</sub>.
  3. Connect the AV<sub>SS</sub> pin to V<sub>SS</sub>.
  4. The SCL0 and SDA0 pins are available in the μPD78F4216AY, 78F4218AY only.
  5. The EXA pin is available in the μPD78F4218A, 78F4218AY only.

A0 to A19:	Address Bus	P120 to P127:	Port 12
AD0 to AD7:	Address/Data Bus	P130, P131:	Port 13
ANI0 to ANI7:	Analog Input	PCL:	Programmable Clock
ANO0, ANO1:	Analog Output	$\overline{RD}$ :	Read Strobe
ASCK1, ASCK2:	Asynchronous Serial Clock	$\overline{RESET}$ :	Reset
ASTB:	Address Strobe	RTP0 to RTP7:	Real-time Output Port
AVDD:	Analog Power Supply	RxD1, RxD2:	Receive Data
AVREF0, AVREF1:	Analog Reference Voltage	$\overline{SCK0}$ to $\overline{SCK2}$ :	Serial Clock
AVSS:	Analog Ground	SCL0 <sup>Note 1</sup> :	Serial Clock
BUZ:	Buzzer Clock	SDA0 <sup>Note 1</sup> :	Serial Data
EXA <sup>Note 2</sup> :	External Access Status Output	SI0 to SI2:	Serial Input
INTP0 to INTP6:	Interrupt from Peripherals	SO0 to SO2:	Serial Output
NMI:	Non-maskable Interrupt	TI00, TI01, TI1, TI2, TI5 to TI8:	Timer Input
P00 to P06:	Port 0	TO0 to TO2, TO5 to TO8:	Timer Output
P10 to P17:	Port 1	TxD1, TxD2:	Transmit Data
P20 to P27:	Port 2	VDD:	Power Supply
P30 to P37:	Port 3	VPP:	Programming Power Supply
P40 to P47:	Port 4	VSS:	Ground
P50 to P57:	Port 5	$\overline{WAIT}$ :	Wait
P60 to P67:	Port 6	$\overline{WR}$ :	Write Strobe
P70 to P72:	Port 7	X1, X2:	Crystal (Main System Clock)
P80 to P87:	Port 8	XT1, XT2:	Crystal (Subsystem Clock)
P90 to P95:	Port 9		
P100 to P103:	Port 10		

**Notes** 1. The SCL0 and SDA0 pins are available in the μPD78F4216AY, 78F4218AY only.

2. The EXA pin is available in the μPD78F4218A, 78F4218AY only.

3. BLOCK DIAGRAM



- Notes**
1. This function supports the I<sup>2</sup>C bus interface and is available in the μPD78F4216AY, 78F4218AY only.
  2. The EXA pin is available in the μPD78F4218A, 78F4218AY only.

## 4. PIN FUNCTIONS

### 4.1 Port Pins (1/2)

Pin Name	I/O	Alternate Function	Function
P00	I/O	INTP0	Port 0 (P0): <ul style="list-style-type: none"> <li>• 7-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• Whether specifying input mode or output mode, an on-chip pull-up resistor can be specified in 1-bit units by means of software.</li> </ul>
P01		INTP1	
P02		INTP2/NMI	
P03		INTP3	
P04		INTP4	
P05		INTP5	
P06		INTP6	
P10 to P17	Input	ANI0 to ANI7	Port 1 (P1): <ul style="list-style-type: none"> <li>• 8-bit input only port</li> </ul>
P20	I/O	RxD1/SI1	Port 2 (P2): <ul style="list-style-type: none"> <li>• 8-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• Whether specifying input mode or output mode, an on-chip pull-up resistor can be specified in 1-bit units by means of software.</li> </ul>
P21		TxD1/SO1	
P22		ASCK1/ $\overline{\text{SCK1}}$	
P23		PCL	
P24		BUZ	
P25		SI0/SDA0 <sup>Note 1</sup>	
P26		SO0	
P27		$\overline{\text{SCK0}}$ /SCL0 <sup>Note 1</sup>	
P30	I/O	TO0	Port 3 (P3): <ul style="list-style-type: none"> <li>• 8-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• Whether specifying input mode or output mode, an on-chip pull-up resistor can be specified in 1-bit units by means of software.</li> </ul>
P31		TO1	
P32		TO2	
P33		TI1	
P34		TI2	
P35		TI00	
P36		TI01	
P37		EXA <sup>Note 2</sup>	
P40 to P47	I/O	AD0 to AD7	Port 4 (P4): <ul style="list-style-type: none"> <li>• 8-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• When used as an input port, an on-chip pull-up resistor can be specified by means of software.</li> <li>• LEDs can be driven directly.</li> </ul>
P50 to P57	I/O	A8 to A15	Port 5 (P5): <ul style="list-style-type: none"> <li>• 8-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• When used as an input port, an on-chip pull-up resistor can be specified by means of software.</li> <li>• LEDs can be driven directly.</li> </ul>

**Notes** 1. This SDA0 and SCL0 are available in the μPD78F4216AY, 78F4218AY only.

2. This function is available in the μPD78F4218A, 784218AY only.

4.1 Port Pins (2/2)

Pin Name	I/O	Alternate Function	Function
P60	I/O	A16	Port 6 (P6): <ul style="list-style-type: none"> <li>• 8-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• When used as an input port, an on-chip pull-up resistor can be specified by means of software.</li> </ul>
P61		A17	
P62		A18	
P63		A19	
P64		$\overline{RD}$	
P65		$\overline{WR}$	
P66		$\overline{WAIT}$	
P67		ASTB	
P70	I/O	RxD2/SI2	Port 7 (P7): <ul style="list-style-type: none"> <li>• 3-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• Whether specifying input mode or output mode, an on-chip pull-up resistor can be specified in 1-bit units by means of software.</li> </ul>
P71		TxD2/SO2	
P72		ASCK2/ $\overline{SCK2}$	
P80 to P87	I/O	A0 to A7	Port 8 (P8): <ul style="list-style-type: none"> <li>• 8-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• Whether specifying input mode or output mode, an on-chip pull-up resistor can be specified in 1-bit units by means of software.</li> <li>• The interrupt control flag (KRIF) is set to 1 when a falling edge is detected at a pin of this port.</li> </ul>
P90 to P95	I/O	–	Port 9 (P9): <ul style="list-style-type: none"> <li>• N-ch open-drain middle-voltage I/O port</li> <li>• 6-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• LEDs can be driven directly.</li> </ul>
P100	I/O	TI5/TO5	Port 10 (P10): <ul style="list-style-type: none"> <li>• 4-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• Whether specifying input mode or output mode, an on-chip pull-up resistor can be specified in 1-bit units by means of software.</li> </ul>
P101		TI6/TO6	
P102		TI7/TO7	
P103		TI8/TO8	
P120 to P127	I/O	RTP0 to RTP7	Port 12 (P12): <ul style="list-style-type: none"> <li>• 8-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> <li>• Whether specifying input mode or output mode, an on-chip pull-up resistor can be specified in 1-bit units by means of software.</li> </ul>
P130, P131	I/O	ANO0, ANO1	Port 13 (P13): <ul style="list-style-type: none"> <li>• 2-bit I/O port</li> <li>• Input/output can be specified in 1-bit units.</li> </ul>

4.2 Non-Port Pins (1/2)

Pin Name	I/O	Alternate Function	Function	
TI00	Input	P35	External count clock input to 16-bit timer counter	
TI01		P36	Capture trigger signal input to capture/compare register 00	
TI1		P33	External count clock input to 8-bit timer counter 1	
TI2		P34	External count clock input to 8-bit timer counter 2	
TI5		P100/TO5	External count clock input to 8-bit timer counter 5	
TI6		P101/TO6	External count clock input to 8-bit timer counter 6	
TI7		P102/TO7	External count clock input to 8-bit timer counter 7	
TI8		P103/TO8	External count clock input to 8-bit timer counter 8	
TO0	Output	P30	16-bit timer output (shared by 14-bit PWM output)	
TO1		P31	8-bit timer output (shared by 8-bit PWM output)	
TO2		P32		
TO5		P100/TI5		
TO6		P101/TI6		
TO7		P102/TI7		
TO8		P103/TI8		
RxD1		Input		P20/SI1
RxD2	P70/SI2			Serial data input (UART2)
TxD1	Output	P21/SO1	Serial data output (UART1)	
TxD2		P71/SO2	Serial data output (UART2)	
ASCK1	Input	P22/ $\overline{\text{SCK}}1$	Baud rate clock input (UART1)	
ASCK2		P72/ $\overline{\text{SCK}}2$	Baud rate clock input (UART2)	
SI0	Input	P25/SDA0 <sup>Note</sup>	Serial data input (3-wire serial I/O 0)	
SI1		P20/RxD1	Serial data input (3-wire serial I/O 1)	
SI2		P70/RxD2	Serial data input (3-wire serial I/O 2)	
SO0	Output	P26	Serial data output (3-wire serial I/O 0)	
SO1		P21/TxD1	Serial data output (3-wire serial I/O 1)	
SO2		P71/TxD2	Serial data output (3-wire serial I/O 2)	
SDA0 <sup>Note</sup>	I/O	P25/SI0	Serial data input/output (I <sup>2</sup> C bus)	
$\overline{\text{SCK}}0$		P27/SCL0 <sup>Note</sup>	Serial clock input/output (3-wire serial I/O 0)	
$\overline{\text{SCK}}1$		P22/ASCK1	Serial clock input/output (3-wire serial I/O 1)	
$\overline{\text{SCK}}2$		P72/ASCK2	Serial clock input/output (3-wire serial I/O 2)	
SCL0 <sup>Note</sup>		P27/ $\overline{\text{SCK}}0$	Serial clock input/output (I <sup>2</sup> C bus)	
NMI	Input	P02/INTP2	Non-maskable interrupt request input	
INTP0		P00	External interrupt request input	
INTP1		P01		
INTP2		P02/NMI		
INTP3		P03		
INTP4		P04		
INTP5		P05		
INTP6		P06		

**Note** This function is available in the μPD78F4216AY, 78F4218AY only.

4.2 Non-Port Pins (2/2)

Pin Name	I/O	Alternate Function	Function
PCL	Output	P23	Clock output (for trimming main system clock and subsystem clock)
BUZ	Output	P24	Buzzer output
RTP0 to RTP7	Output	P120 to P127	Real-time output port that outputs data in synchronization with trigger
AD0 to AD7	I/O	P40 to P47	Lower address/data bus for expanding memory externally
A0 to A7	Output	P80 to P87	Lower address bus for expanding memory externally
A8 to A15		P50 to P57	Middle address bus for expanding memory externally
A16 to A19		P60 to P63	Higher address bus for expanding memory externally
$\overline{RD}$	Output	P64	Strobe signal output for reading from external memory
$\overline{WR}$		P65	Strobe signal output for writing to external memory
$\overline{WAIT}$	Input	P66	Wait insertion at external memory access
ASTB	Output	P67	Strobe output that externally latches address information output to ports 4 through 6 and 8 to access external memory
EXA <sup>Note</sup>	Output	P37	Status signal output at external memory access
$\overline{RESET}$	Input	–	System reset input
X1	Input	–	Connecting crystal resonator for main system clock oscillation
X2	–		
XT1	Input		
XT2	–	–	Connecting crystal resonator for subsystem clock oscillation
ANI0 to ANI7	Input	P10 to P17	A/D converter analog input
ANO0, ANO1	Output	P130, P131	D/A converter analog output
AVREF0	–	–	A/D converter reference voltage input
AVREF1			D/A converter reference voltage input
AVDD			A/D converter positive power supply. Connect to V <sub>DD</sub> .
AVSS			GND for A/D converter and D/A converter. Connect to V <sub>SS</sub> .
VDD			Positive power supply
VSS			GND
VPP			Flash memory programming mode setting. Applying high-voltage for program write/verify. Connect this pin to V <sub>SS</sub> directly or via a pull-down resistor in normal operation mode. Connect the V <sub>PP</sub> pin to V <sub>SS</sub> via a pull-down resistor in a system in which the on-chip flash memory is written while mounted on the target board. For the pull-down connection, it is recommended to use a resistor with a resistance ranging from 470 Ω to 10 kΩ.

**Note** The EXA pin is available in the μPD78F4218A, 78F4218AY only.

### 4.3 Pin I/O Circuits and Recommended Connections of Unused Pins

The I/O circuit type of each pin and recommended connections of unused pins are shown in Table 4-1. For each type of input/output circuit, refer to Figure 4-1.

**Table 4-1. Types of Pin I/O Circuits and Recommended Connection of Unused Pins (1/2)**

Pin Name	I/O Circuit Type	I/O	Recommended Connection of Unused Pins
P00/INTP0	8-N	I/O	Input: Independently connect to V <sub>SS</sub> via a resistor Output: Leave open
P01/INTP1			
P02/INTP2/NMI			
P03/INTP3 to P06/INTP6			
P10/ANI0 to P17/ANI7	9	Input	Connect to V <sub>SS</sub> or V <sub>DD</sub>
P20/RxD1/SI1	10-K	I/O	Input: Independently connect to V <sub>SS</sub> via a resistor Output: Leave open
P21/TxD1/SO1	10-L		
P22/ASCK1/SCK1	10-K		
P23/PCL	10-L		
P24/BUZ			
P25/SI0/SDA0 <sup>Note 1</sup>	10-K		
P26/SO0	10-L		
P27/SCK0/SCL0 <sup>Note 1</sup>	10-K		
P30/TO0 to P32/TO2	12-E		
P33/TI1, P34/TI2	8-N		
P35/TI00, P36/TI01	10-M		
P37/EXA <sup>Note 2</sup>	12-E		
P40/AD0 to P47/AD7	5-A		
P50/A8 to P57/A15			
P60/A16 to P63/A19			
P64/RD			
P65/WR			
P66/WAIT			
P67/ASTB			
P70/RxD2/SI2	8-N		
P71/TxD2/SO2	10-M		
P72/ASCK2/SCK2	8-N		
P80/A0 to P87/A7	12-E		
P90 to P95	13-D		
P100/TI5/TO5	8-N		
P101/TI6/TO6			
P102/TI7/TO7			
P103/TI8/TO8			
P120/RTP0 to P127/RTP7	12-E		
P130/ANO0, P131/ANO1	12-F		

**Notes** 1. The SDA0 and SCL0 pins are available in the μPD78F4216AY, 78F4218AY only.

2. The EXA pin is available in the μPD78F4218A, 78F4218AY only.



Table 4-1. Types of Pin I/O Circuits and Recommended Connection of Unused Pins (2/2)

Pin Name	I/O Circuit Type	I/O	Recommended Connection of Unused Pins
RESET	2-G	Input	–
XT1	16	–	Connect to V <sub>SS</sub>
XT2			Leave open
AV <sub>REF0</sub>	–	–	Connect to V <sub>SS</sub>
AV <sub>REF1</sub>			Connect to V <sub>DD</sub>
AV <sub>DD</sub>			
AV <sub>SS</sub>			Connect to V <sub>SS</sub>
V <sub>PP</sub>			Connect this pin to V <sub>SS</sub> directly or via a pull-down resist in normal operation mode. Connect the V <sub>PP</sub> pin to V <sub>SS</sub> via a pull-down resistor in a system in which the on-chip flash memory is written while mounted on the target board. For the pull-down connection, it is recommended to use a resistor with a resistance ranging from 470 Ω to 10 kΩ.

**Remark** Because the circuit type numbers are standardized among the 78K Series products, they are not sequential in some models (i.e., some circuits are not provided).

Figure 4-1. Types of Pin I/O Circuits (1/2)

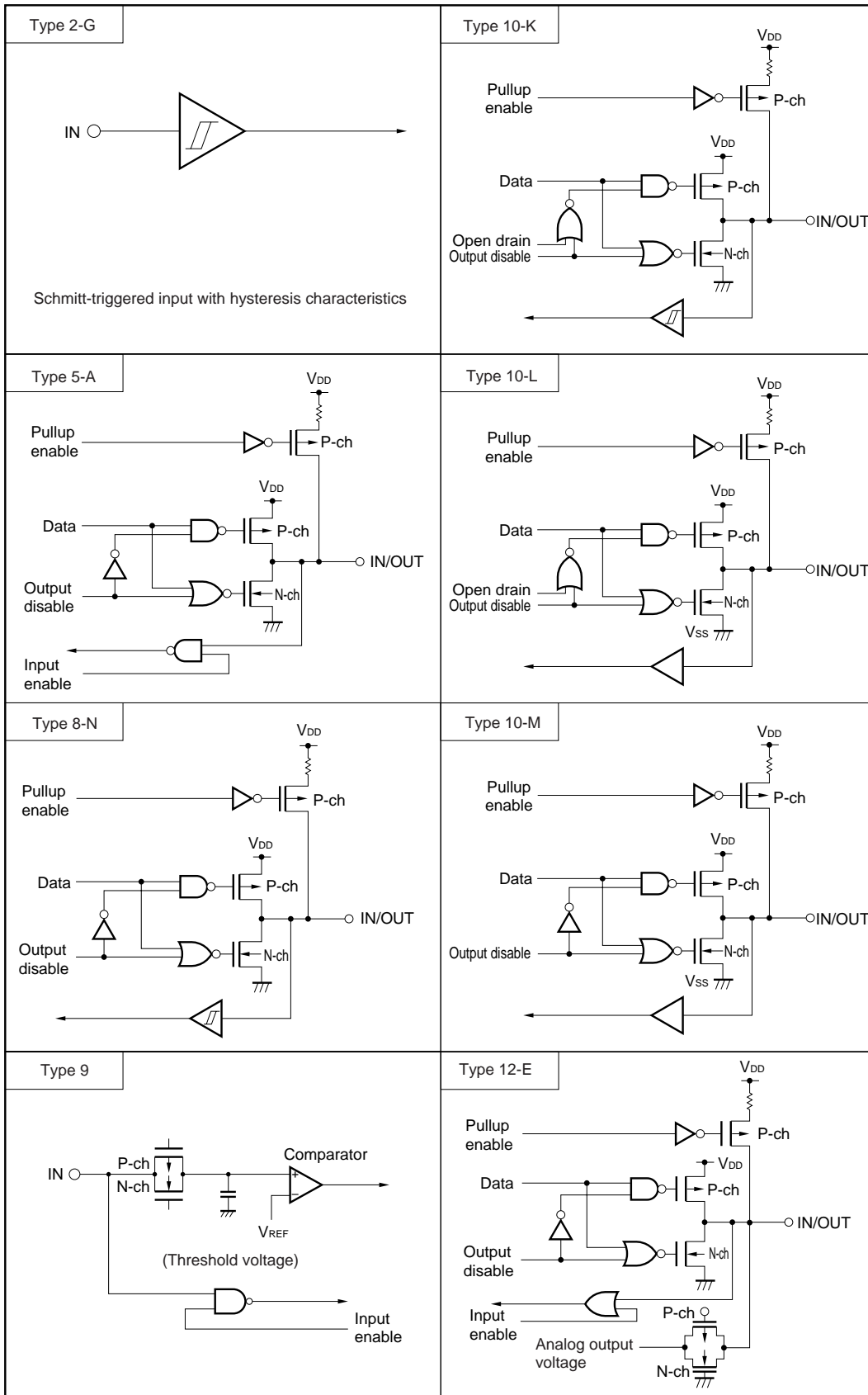
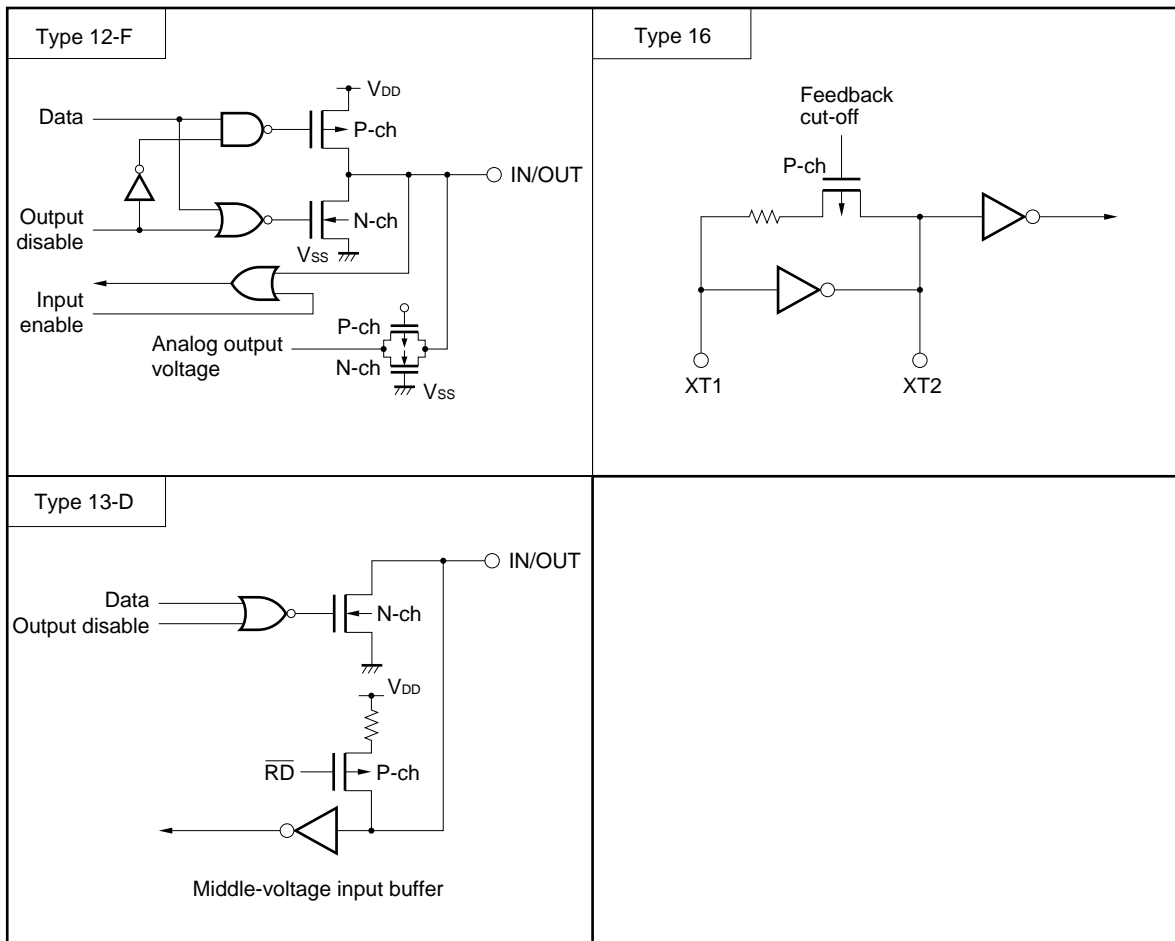


Figure 4-1. Types of Pin I/O Circuits (2/2)



5. INTERNAL MEMORY SIZE SWITCHING REGISTER (IMS)

IMS is a register that is set by software and is used to specify a part of the internal memory that is not to be used. By setting this register, the internal memory of the μPD78F4218AY can be mapped identically to that of a mask ROM version with a different internal memory (ROM and RAM) capacity.

IMS is set with an 8-bit memory manipulation instruction.

RESET input sets IMS to FFH.

(1) μPD78F4216A, 78F4216AY

Figure 5-1. Internal Memory Size Switching Register (IMS) Format

Address: 0FFFCH      After reset: FFH      W

	7	6	5	4	3	2	1	0
IMS	1	1	ROM1	ROM0	1	1	RAM1	RAM0

ROM1	ROM0	Internal ROM Capacity Selection
0	0	48 KB
0	1	64 KB
1	0	96 KB
1	1	128 KB

RAM1	RAM0	Peripheral RAM Capacity Selection
0	0	3,072 bytes
0	1	4,608 bytes
1	0	6,114 bytes
1	1	7,680 bytes

**Caution** IMS is not provided on the mask ROM versions (μPD784214A, 784215A, 784216A, μPD784214AY, 784215AY, and 784216AY).

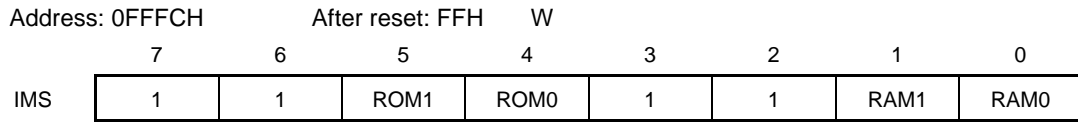
Table 5-1 shows the IMS setting values to make the memory mapping the same as that of the mask ROM versions.

Table 5-1. Setting Value of Internal Memory Size Switching Register (IMS)

Target Mask ROM Version	IMS Setting Value
μPD784214A, 784214AY	ECH
μPD784215A, 784215AY	FDH
μPD784216A, 784216AY	FFH

(2) μPD78F4218A, 78F4218AY

Figure 5-2. Internal Memory Size Switching Register (IMS) Format



ROM1	ROM0	Internal ROM Capacity Selection
0	0	64 KB
0	1	128 KB
1	0	192 KB
1	1	256 KB

RAM1	RAM0	Peripheral RAM Capacity Selection
0	0	3,072 bytes
0	1	6,656 bytes
1	0	7,168 bytes
1	1	12,288 bytes

**Caution** IMS is not provided on the mask ROM versions (μPD784217A, 784218A, 784217AY, and 784218AY).

Table 5-2 shows the IMS setting values to make the memory mapping the same as that of the mask ROM versions.

Table 5-2. Setting Value of Internal Memory Size Switching Register (IMS)

Target Mask ROM Version	IMS Setting Value
μPD784217A, 784217AY	EFH
μPD784218A, 784218AY	FFH

**6. PROGRAMMING FLASH MEMORY**

The flash memory can be written with the μPD78F4218AY mounted on the target board (on-board). To do so, connect a dedicated flash programmer (Flashpro II (part number: FL-PR2), Flashpro III (part number: FL-PR3, PG-FP3) to the host machine and target system.

Writing to flash memory can also be performed using flash memory writing adapter connected to Flashpro II or Flashpro III.

**Remark** FL-PR2 and FL-PR3 are products of Naito Densai Machida Mfg. Co., Ltd.

**6.1 Selecting Communication Mode**

To write the flash memory, use Flashpro II and Flashpro III by serial communication. Select a serial communication mode from those listed in Table 6-1 in the format shown in Figure 6-1. Each communication mode is selected by the number of V<sub>PP</sub> pulses shown in Table 6-1.

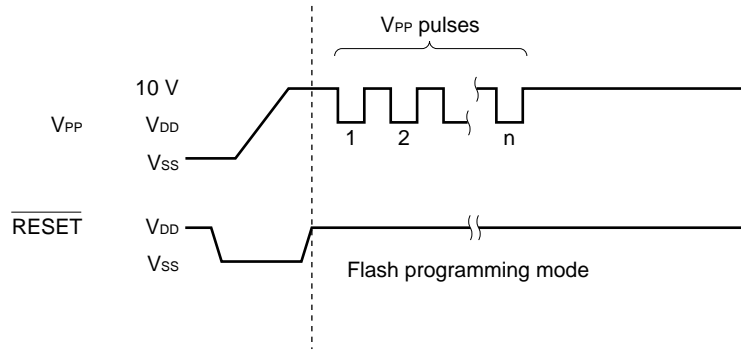
**Table 6-1. Communication Modes**

Communication Mode	Number of Channels	Pins Used	Number of V <sub>PP</sub> Pulses
3-wire serial I/O	3	SCK0/P27/SCL0 <sup>Note 1</sup> SO0/P26 SI0/P25/SDA0 <sup>Note 1</sup>	0
		SCK1/ASCK1/P22 SO1/TxD1/P21 SI1/RxD1/P20	1
		SCK2/ASCK2/P72 SO2/TxD2/P71 SI2/RxD2/P70	2
Handshake <sup>Note 2</sup>	1	SCK0/P27/SCL0 <sup>Note 1</sup> SO0/P26 SI0/P25/SDA0 <sup>Note 1</sup> P24/BUZ	3
UART	2	TxD1/SO1/P21 RxD1/SI1/P20	8
		TxD2/SO2/P71 RxD2/SI2/P70	9

- Notes**
1. The SCL0 and SDA0 pins are available in the μPD78F4216AY, 78F4218AY only.
  2. This made is available in the μPD78F4216A, 78F4216AY (other than I, K, E standard)  
This made is available in the μPD78F4218A, 78F4218AY (other than I standard)

**Caution** Be sure to select a communication mode with the number of V<sub>PP</sub> pulses shown in Table 6-1.

Figure 6-1. Communication Mode Selecting Format



## 6.2 Flash Memory Programming Function

The flash memory is written by transferring or receiving commands and data in a selected communication mode. The major functions of flash memory programming are listed in Table 6-2.

Table 6-2. Major Functions of Flash Memory Programming

Function	Description
Batch erasure	Erases all contents of memory.
Block erasure	Erases contents of specified memory block with one memory block consisting of 16 KB.
Batch blank check	Checks erased status of entire memory.
Block blank check	Checks erased status of specified block.
Data write	Writes flash memory based on write start address and number of data to be written (in bytes).
Batch verify	Compares all contents of memory with input data.
Block verify	Compares contents of specified memory block with input data.

### 6.3 Connecting Flashpro II and Flashpro III

The Flashpro II, Flashpro III and μPD78F4218AY are connected differently depending on the selected communication mode (3-wire serial I/O or UART). Figures 6-2 to 6-4 show the connections in the respective communication modes.

Figure 6-2. Connection of Flashpro II and Flashpro III in 3-Wire Serial I/O Mode

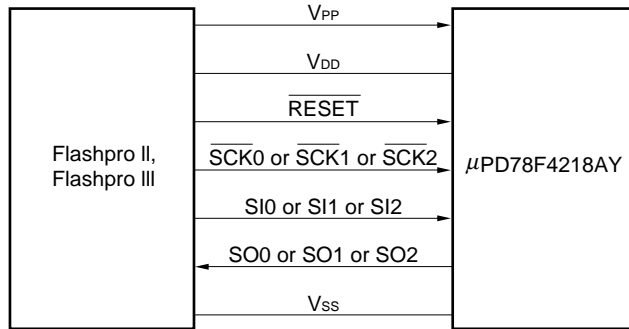


Figure 6-3. Connection of Flashpro III in Handshake Mode

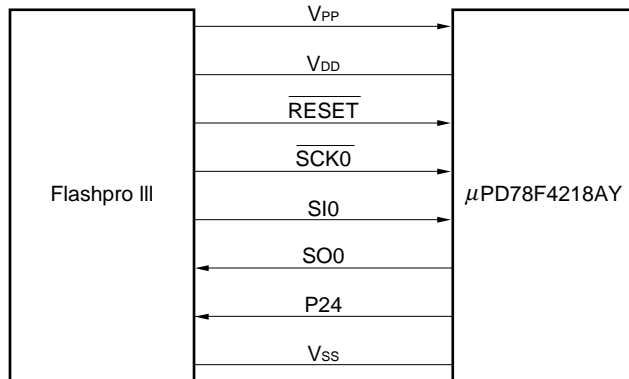
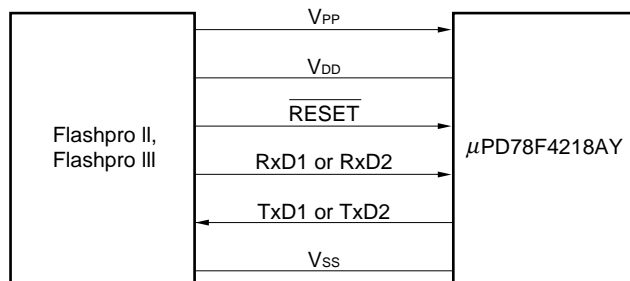


Figure 6-4. Connection of Flashpro II and Flashpro III in UART Mode





7. ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings (T<sub>A</sub> = 25°C)

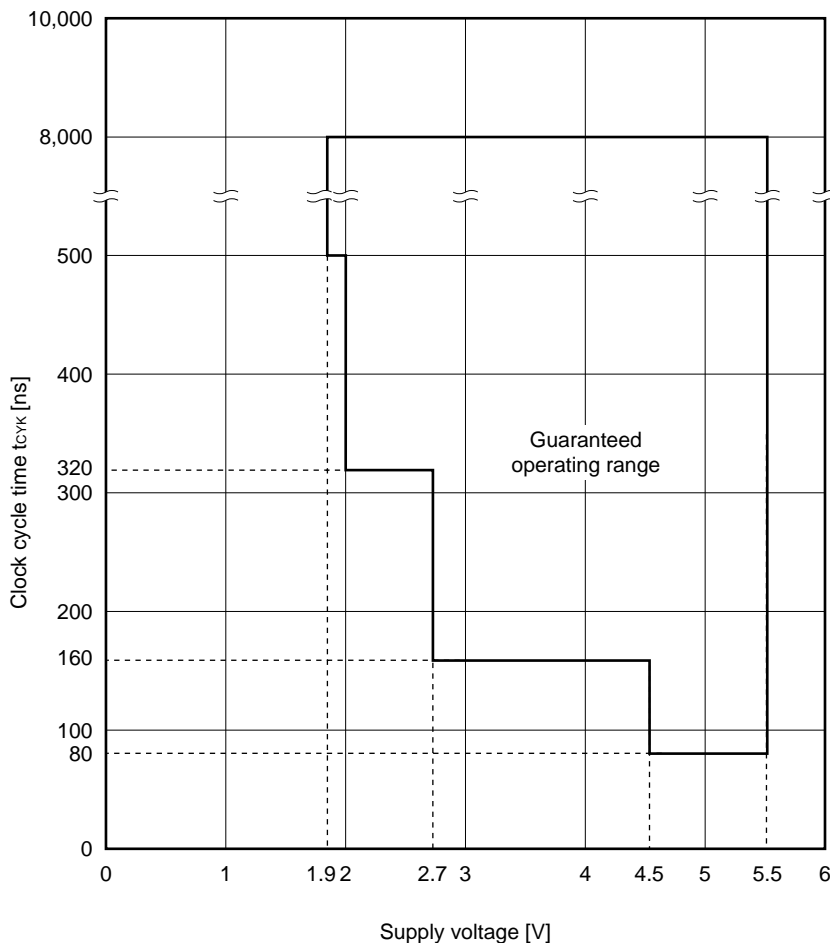
Parameter	Symbol	Conditions	Ratings	Unit	
Supply voltage	V <sub>DD</sub>		-0.3 to +6.5	V	
	AV <sub>DD</sub>		-0.3 to V <sub>DD</sub> + 0.3	V	
	AV <sub>SS</sub>		-0.3 to V <sub>SS</sub> + 0.3	V	
	AV <sub>REF0</sub>	A/D converter reference voltage input	-0.3 to V <sub>DD</sub> + 0.3	V	
	AV <sub>REF1</sub>	D/A converter reference voltage input	-0.3 to V <sub>DD</sub> + 0.3	V	
Input voltage	V <sub>I1</sub>	Other than P90 to P95	-0.3 to V <sub>DD</sub> + 0.3	V	
	V <sub>I2</sub>	P90 to P95	N-ch open drain	-0.3 to +12	V
	V <sub>I3</sub>	V <sub>PP</sub> pin for programming		-0.3 to +10.5	V
Analog input voltage	V <sub>AN</sub>	Analog input pin	AV <sub>SS</sub> - 0.3 to AV <sub>REF0</sub> + 0.3	V	
Output voltage	V <sub>O</sub>		-0.3 to V <sub>DD</sub> + 0.3	V	
Output current, low	I <sub>OL</sub>	Per pin	15	mA	
		Total of P2, P4 to P8	75	mA	
		Total of P0, P3, P9, P10, P12, P13	75	mA	
		Total of all pins	100	mA	
Output current, high	I <sub>OH</sub>	Per pin	-10	mA	
		Total of all pins	-50	mA	
Operating ambient temperature	T <sub>A</sub>		-40 to +85	°C	
Storage temperature	T <sub>stg</sub>		-65 to +125	°C	

**Caution** Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

**Operating Conditions**

- Operating ambient temperature (T<sub>A</sub>): -40 to +85°C
- Supply voltage and clock cycle time: See Figure 7-1
- Operating voltage with subsystem clock operation: V<sub>DD</sub> = 1.9 to 5.5 V

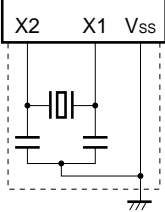
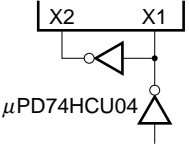
**Figure 7-1. Supply Voltage and Clock Cycle Time (CPU Clock Frequency: f<sub>CPU</sub>)**



**Capacitance (T<sub>A</sub> = 25°C, V<sub>DD</sub> = V<sub>SS</sub> = 0 V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input capacitance	C <sub>i</sub>	f = 1 MHz Unmeasured pins returned to 0 V.	Other than Port 9			15	pF
			Port 9			20	pF
Output capacitance	C <sub>o</sub>		Other than Port 9			15	pF
			Port 9			20	pF
I/O capacitance	C <sub>io</sub>		Other than Port 9			15	pF
			Port 9			20	pF

**Main System Clock Oscillator Characteristics (T<sub>A</sub> = -40 to +85°C)**

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Ceramic resonator or crystal resonator		Oscillation frequency (f <sub>x</sub> )	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	2		12.5	MHz
			2.7 V ≤ V <sub>DD</sub> < 4.5 V	2		6.25	
			2.0 V ≤ V <sub>DD</sub> < 2.7 V	2		3.125	
			1.9 V ≤ V <sub>DD</sub> < 2.0 V	2		2	
External clock		X1 input frequency (f <sub>x</sub> )	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	2		12.5	MHz
			2.7 V ≤ V <sub>DD</sub> < 4.5 V	2		6.25	
			2.0 V ≤ V <sub>DD</sub> < 2.7 V	2		3.125	
			1.9 V ≤ V <sub>DD</sub> < 2.0 V	2		2	
		X1 input high-/low-level width (t <sub>wXH</sub> , t <sub>wXL</sub> )		15		250	ns
		X1 input rising/falling time (t <sub>xR</sub> , t <sub>xF</sub> )	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		5	ns
			2.7 V ≤ V <sub>DD</sub> < 4.5 V	0		10	
			2.0 V ≤ V <sub>DD</sub> < 2.7 V	0		20	
1.9 V ≤ V <sub>DD</sub> < 2.0 V	0			30			

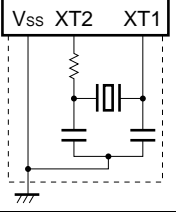
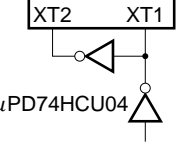
**Cautions 1.** When using the main system clock oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- Keep the wiring length as short as possible.
- Do not cross the wiring with other signal lines.
- Do not route the wiring near a signal line through which a high fluctuating current flows.
- Always make the ground point of the oscillator capacitor the same potential as V<sub>ss</sub>.
- Do not ground the capacitor to a ground pattern through which a high current flows.
- Do not fetch signals from the oscillator.

**2.** When the main system clock is stopped and the system is operated by the subsystem clock, the subsystem clock should be switched back to the main system clock after the oscillation stabilization time is secured by the program.

**Remark** For the resonator selection and oscillator constant, users are required to either evaluate the oscillation themselves or apply to the resonator manufacturer for evaluation.

**Subsystem Clock Oscillator Characteristics (T<sub>A</sub> = -40 to +85°C)**

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Crystal resonator		Oscillation frequency (f <sub>XT</sub> )		32	32.768	35	kHz
		Oscillation stabilization time <sup>Note</sup>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V		1.2	2	s
		1.9 V ≤ V <sub>DD</sub> < 4.5 V			10		
External clock		XT1 input frequency (f <sub>XT</sub> )		32		35	kHz
		XT1 input high-/low-level width (t <sub>XTH</sub> , t <sub>XTL</sub> )		14.3		15.6	μs

**Note** Time required to stabilize oscillation after applying supply voltage (V<sub>DD</sub>).

**Cautions** 1. When using the subsystem clock oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- Keep the wiring length as short as possible.
- Do not cross the wiring with other signal lines.
- Do not route the wiring near a signal line through which a high fluctuating current flows.
- Always make the ground point of the oscillator capacitor the same potential as V<sub>SS</sub>.
- Do not ground the capacitor to a ground pattern through which a high current flows.
- Do not fetch signals from the oscillator.

2. When the main system clock is stopped and the device is operating on the subsystem clock, wait until the oscillation stabilization time has been secured by the program before switching back to the main system clock.

**Remark** For the resonator selection and oscillator constant, users are required to either evaluate the oscillation themselves or apply to the resonator manufacturer for evaluation.

DC Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V) (1/3)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input voltage, low	V <sub>IL1</sub>	<b>Note 1</b>	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		0.3V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0		0.2V <sub>DD</sub>	
	V <sub>IL2</sub>	P00 to P06, P20, P22, P33, P34, P70, P72, P100 to P103, RESET	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		0.2V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0		0.15V <sub>DD</sub>	
	V <sub>IL3</sub>	P90 to P95 (N-ch open drain)	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		0.3V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0		0.2V <sub>DD</sub>	
	V <sub>IL4</sub>	P10 to P17, P130, P131	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		0.3V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0		0.2V <sub>DD</sub>	
	V <sub>IL5</sub>	X1, X2, XT1, XT2	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		0.2V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0		0.1V <sub>DD</sub>	
	V <sub>IL6</sub>	P25, P27	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		0.3V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0		0.2V <sub>DD</sub>	
Input voltage, high	V <sub>IH1</sub>	<b>Note 1</b>	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0.7V <sub>DD</sub>		V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0.8V <sub>DD</sub>		V <sub>DD</sub>	
	V <sub>IH2</sub>	P00 to P06, P20, P22, P33, P34, P70, P72, P100 to P103, RESET	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0.8V <sub>DD</sub>		V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0.85V <sub>DD</sub>		V <sub>DD</sub>	
	V <sub>IH3</sub>	P90 to P95 (N-ch open drain)	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0.7V <sub>DD</sub>		12	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0.8V <sub>DD</sub>		V <sub>DD</sub>	
	V <sub>IH4</sub>	P10 to P17, P130, P131	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0.7V <sub>DD</sub>		V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0.8V <sub>DD</sub>		V <sub>DD</sub>	
	V <sub>IH5</sub>	X1, X2, XT1, XT2	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0.8V <sub>DD</sub>		V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0.85V <sub>DD</sub>		V <sub>DD</sub>	
	V <sub>IH6</sub>	P25, P27	2.2 V ≤ V <sub>DD</sub> ≤ 5.5 V	0.7V <sub>DD</sub>		V <sub>DD</sub>	V
			1.9 V ≤ V <sub>DD</sub> < 2.2 V	0.8V <sub>DD</sub>		V <sub>DD</sub>	
Output voltage, low	V <sub>OL1</sub>	For pins other than P40 to P47, P50 to P57, P90 to P95 I <sub>OL</sub> = 1.6 mA <sup>Note 1</sup>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V			0.4	V
		P40 to P47, P50 to P57 I <sub>OL</sub> = 8 mA <sup>Note 2</sup>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V			1.0	
		P90 to P95 I <sub>OL</sub> = 15 mA <sup>Note 2</sup>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V		0.8	2.0	
	V <sub>OL2</sub>	I <sub>OL</sub> = 400 μA <sup>Note 2</sup>				0.5	V
Output voltage, high	V <sub>OH1</sub>	I <sub>OH</sub> = -1 mA <sup>Note 2</sup>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	V <sub>DD</sub> - 1.0			V
		I <sub>OH</sub> = -100 μA <sup>Note 2</sup>		V <sub>DD</sub> - 0.5			V
Input leakage current, low	I <sub>LIL1</sub>	V <sub>IN</sub> = 0 V	Except X1, X2, XT1 XT2			-3	μA
	I <sub>LIL2</sub>		X1, X2, XT1, XT2			-20	μA
Input leakage current, high	I <sub>LIH1</sub>	V <sub>IN</sub> = V <sub>DD</sub>	Except X1, X2, XT1 XT2			3	μA
	I <sub>LIH2</sub>		X1, X2, XT1, XT2			20	μA
	I <sub>LIH3</sub>	V <sub>IN</sub> = 12 V (N-ch open drain)	P90 to P95			20	μA
Output leakage current, low	I <sub>LOL1</sub>	V <sub>OUT</sub> = 0 V				-3	μA
Output leakage current, high	I <sub>LOH1</sub>	V <sub>OUT</sub> = V <sub>DD</sub>				3	μA

**Notes** 1. P21, P23, P24, P26, P30 to P32, P35 to P37, P40 to P47, P50 to P57, P60 to P67, P71, P80 to P87, P120 to P127

2. Per pin

DC Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V) (2/3)

(1) μPD78F4216A, 78F4216AY

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Supply voltage	I <sub>DD1</sub>	Operation mode	f <sub>XX</sub> = 12.5 MHz, V <sub>DD</sub> = 5.0 V ±10%		17	40	mA
			f <sub>XX</sub> = 6 MHz, V <sub>DD</sub> = 3.0 V ±10%		5	17	mA
			f <sub>XX</sub> = 2 MHz, V <sub>DD</sub> = 2.0 V ±5%		2	10	mA
	I <sub>DD2</sub>	HALT mode	f <sub>XX</sub> = 12.5 MHz, V <sub>DD</sub> = 5.0 V ±10%		6	20	mA
			f <sub>XX</sub> = 6 MHz, V <sub>DD</sub> = 3.0 V ±10%		2	10	mA
			f <sub>XX</sub> = 2 MHz, V <sub>DD</sub> = 2.0 V ±5%		0.4	7	mA
	I <sub>DD3</sub>	IDLE mode	f <sub>XX</sub> = 12.5 MHz, V <sub>DD</sub> = 5.0 V ±10%		1	3	mA
			f <sub>XX</sub> = 6 MHz, V <sub>DD</sub> = 3.0 V ±10%		0.5	1.3	mA
			f <sub>XX</sub> = 2 MHz, V <sub>DD</sub> = 2.0 V ±5%		0.3	0.9	mA
	I <sub>DD4</sub>	Operation mode <sup>Note</sup>	f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 5.0 V ±10%		130	500	μA
			f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 3.0 V ±10%		90	350	μA
			f <sub>XX</sub> = 32 kHz, 2.0 V ≤ V <sub>DD</sub> ≤ 2.7 V		80	300	μA
			f <sub>XX</sub> = 32 kHz, 1.9 V ≤ V <sub>DD</sub> < 2.0 V		70	250	μA
	I <sub>DD5</sub>	HALT mode <sup>Note</sup>	f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 5.0 V ±10%		60	200	μA
			f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 3.0 V ±10%		20	160	μA
			f <sub>XX</sub> = 32 kHz, 2.0 V ≤ V <sub>DD</sub> ≤ 2.7 V		15	120	μA
f <sub>XX</sub> = 32 kHz, 1.9 V ≤ V <sub>DD</sub> < 2.0 V				10	100	μA	
I <sub>DD6</sub>	IDLE mode <sup>Note</sup>	f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 5.0 V ±10%		50	190	μA	
		f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 3.0 V ±10%		15	150	μA	
		f <sub>XX</sub> = 32 kHz, 2.0 V ≤ V <sub>DD</sub> ≤ 2.7 V		12	110	μA	
		f <sub>XX</sub> = 32 kHz, 1.9 V ≤ V <sub>DD</sub> < 2.0 V		7	90	μA	
Data retention voltage	V <sub>DDDR</sub>	HALT, IDLE modes	1.9		5.5	V	
Data retention current	I <sub>DDDR</sub>	STOP mode	V <sub>DD</sub> = 2.0 V ±5%		2	10	μA
			V <sub>DD</sub> = 5.0 V ±10%		10	50	μA
Pull-up resistor	R <sub>L</sub>	V <sub>IN</sub> = 0 V	10	30	100	kΩ	

**Note** When main system clock is stopped and subsystem clock is operating.

**Remark** Unless otherwise specified, the characteristics of alternate-function pins are the same as those of port pins.

DC Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V) (3/3)

(2) μPD78F4218A, 78F4218AY

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Supply voltage	I <sub>DD1</sub>	Operation mode	f <sub>XX</sub> = 12.5 MHz, V <sub>DD</sub> = 5.0 V ±10%		19	40	mA
			f <sub>XX</sub> = 6 MHz, V <sub>DD</sub> = 3.0 V ±10%		6	17	mA
			f <sub>XX</sub> = 3 MHz, V <sub>DD</sub> = 2.0 V ±5%		2	10	mA
	I <sub>DD2</sub>	HALT mode	f <sub>XX</sub> = 12.5 MHz, V <sub>DD</sub> = 5.0 V ±10%		7	20	mA
			f <sub>XX</sub> = 6 MHz, V <sub>DD</sub> = 3.0 V ±10%		2	10	mA
			f <sub>XX</sub> = 3 MHz, V <sub>DD</sub> = 2.0 V ±5%		0.5	7	mA
	I <sub>DD3</sub>	IDLE mode	f <sub>XX</sub> = 12.5 MHz, V <sub>DD</sub> = 5.0 V ±10%		1	3	mA
			f <sub>XX</sub> = 6 MHz, V <sub>DD</sub> = 3.0 V ±10%		0.5	1.3	mA
			f <sub>XX</sub> = 3 MHz, V <sub>DD</sub> = 2.0 V ±5%		0.3	0.9	mA
	I <sub>DD4</sub>	Operation mode <sup>Note</sup>	f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 5.0 V ±10%		140	500	μA
			f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 3.0 V ±10%		100	350	μA
			f <sub>XX</sub> = 32 kHz, 2.0 V ≤ V <sub>DD</sub> ≤ 2.7 V		90	300	μA
			f <sub>XX</sub> = 32 kHz, 1.9 V ≤ V <sub>DD</sub> < 2.0 V		80	250	μA
	I <sub>DD5</sub>	HALT mode <sup>Note</sup>	f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 5.0 V ±10%		60	200	μA
			f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 3.0 V ±10%		20	160	μA
			f <sub>XX</sub> = 32 kHz, 2.0 V ≤ V <sub>DD</sub> ≤ 2.7 V		15	120	μA
f <sub>XX</sub> = 32 kHz, 1.9 V ≤ V <sub>DD</sub> < 2.0 V				10	100	μA	
I <sub>DD6</sub>	IDLE mode <sup>Note</sup>	f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 5.0 V ±10%		50	190	μA	
		f <sub>XX</sub> = 32 kHz, V <sub>DD</sub> = 3.0 V ±10%		15	150	μA	
		f <sub>XX</sub> = 32 kHz, 2.0 V ≤ V <sub>DD</sub> ≤ 2.7 V		12	110	μA	
		f <sub>XX</sub> = 32 kHz, 1.9 V ≤ V <sub>DD</sub> < 2.0 V		7	90	μA	
Data retention voltage	V <sub>DDDR</sub>	HALT, IDLE modes	1.9		5.5	V	
Data retention current	I <sub>DDDR</sub>	STOP mode	V <sub>DD</sub> = 2.0 V ±5%		2	10	μA
			V <sub>DD</sub> = 5.0 V ±10%		10	50	μA
Pull-up resistor	R <sub>L</sub>	V <sub>IN</sub> = 0 V	10	30	100	kΩ	

**Note** When main system clock is stopped and subsystem clock is operating.

**Remark** Unless otherwise specified, the characteristics of alternate-function pins are the same as those of port pins.

AC Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V)

(1) Read/write operation (1/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Cycle time	t <sub>CYK</sub>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	80			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V	160			ns
		2.0 V ≤ V <sub>DD</sub> < 2.7 V	320			ns
		1.9 V ≤ V <sub>DD</sub> < 2.0 V	500			ns
Address setup time (to ASTB↓)	t <sub>SAST</sub>	V <sub>DD</sub> = 5.0 V ±10%	(0.5 + a)T - 20			ns
		V <sub>DD</sub> = 3.0 V ±10%	(0.5 + a)T - 40			ns
		V <sub>DD</sub> = 2.0 V ±5%	(0.5 + a)T - 80			ns
Address hold time (from ASTB↓)	t <sub>HSTLA</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T - 19			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T - 24			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T - 34			ns
ASTB high-level width	t <sub>WSTH</sub>	V <sub>DD</sub> = 5.0 V ±10%	(0.5 + a)T - 17			ns
		V <sub>DD</sub> = 3.0 V ±10%	(0.5 + a)T - 40			ns
		V <sub>DD</sub> = 2.0 V ±5%	(0.5 + a)T - 110			ns
Address hold time (from RD↑)	t <sub>HRA</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T - 14			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T - 14			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T - 14			ns
Delay time from address to RD↓	t <sub>DAR</sub>	V <sub>DD</sub> = 5.0 V ±10%	(1 + a)T - 24			ns
		V <sub>DD</sub> = 3.0 V ±10%	(1 + a)T - 35			ns
		V <sub>DD</sub> = 2.0 V ±5%	(1 + a)T - 80			ns
Address float time (from RD↓)	t <sub>FAR</sub>	V <sub>DD</sub> = 5.0 V ±10%			0	ns
		V <sub>DD</sub> = 3.0 V ±10%			0	ns
		V <sub>DD</sub> = 2.0 V ±5%			0	ns
Data input time from address	t <sub>DAID</sub>	V <sub>DD</sub> = 5.0 V ±10%			(2.5 + a + n)T - 37	ns
		V <sub>DD</sub> = 3.0 V ±10%			(2.5 + a + n)T - 52	ns
		V <sub>DD</sub> = 2.0 V ±5%			(2.5 + a + n)T - 120	ns
Data input time from ASTB↓	t <sub>DSTID</sub>	V <sub>DD</sub> = 5.0 V ±10%			(2 + n)T - 35	ns
		V <sub>DD</sub> = 3.0 V ±10%			(2 + n)T - 50	ns
		V <sub>DD</sub> = 2.0 V ±5%			(2 + n)T - 80	ns
Data input time from RD↓	t <sub>DRID</sub>	V <sub>DD</sub> = 5.0 V ±10%			(1.5 + n)T - 40	ns
		V <sub>DD</sub> = 3.0 V ±10%			(1.5 + n)T - 50	ns
		V <sub>DD</sub> = 2.0 V ±5%			(1.5 + n)T - 90	ns
Delay time from ASTB↓ to RD↓	t <sub>DSTR</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T - 9			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T - 9			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T - 20			ns
Data hold time (from RD↑)	t <sub>HRID</sub>	V <sub>DD</sub> = 5.0 V ±10%	0			ns
		V <sub>DD</sub> = 3.0 V ±10%	0			ns
		V <sub>DD</sub> = 2.0 V ±5%	0			ns

**Remark** T: t<sub>CYK</sub> = 1/f<sub>XX</sub> (f<sub>XX</sub>: main system clock frequency)

a: 1 (during address wait), otherwise, 0

n: Number of waits (n ≥ 0)



AC Characteristics

(1) Read/write operation (2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Address active time from $\overline{RD}\uparrow$	t <sub>DRA</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T – 2			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T – 12			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T – 35			ns
Delay time from $\overline{RD}\uparrow$ to $\overline{ASTB}\uparrow$	t <sub>DRST</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T – 9			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T – 9			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T – 40			ns
$\overline{RD}$ low-level width	t <sub>WRL</sub>	V <sub>DD</sub> = 5.0 V ±10%	(1.5 + n)T – 25			ns
		V <sub>DD</sub> = 3.0 V ±10%	(1.5 + n)T – 30			ns
		V <sub>DD</sub> = 2.0 V ±5%	(1.5 + n)T – 25			ns
Delay time from address to $\overline{WR}\downarrow$	t <sub>DAW</sub>	V <sub>DD</sub> = 5.0 V ±10%	(1 + a)T – 24			ns
		V <sub>DD</sub> = 3.0 V ±10%	(1 + a)T – 34			ns
		V <sub>DD</sub> = 2.0 V ±5%	(1 + a)T – 70			ns
Address hold time (from $\overline{WR}\uparrow$ )	t <sub>HRD</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T – 14			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T – 14			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T – 14			ns
Delay time from $\overline{ASTB}\downarrow$ to data output	t <sub>DSTOD</sub>	V <sub>DD</sub> = 5.0 V ±10%			0.5T + 15	ns
		V <sub>DD</sub> = 3.0 V ±10%			0.5T + 30	ns
		V <sub>DD</sub> = 2.0 V ±5%			0.5T + 240	ns
Delay time from $\overline{WR}\downarrow$ to data output	t <sub>DWOD</sub>	V <sub>DD</sub> = 5.0 V ±10%			0.5T – 30	ns
		V <sub>DD</sub> = 3.0 V ±10%			0.5T – 30	ns
		V <sub>DD</sub> = 2.0 V ±5%			0.5T – 30	ns
Delay time from $\overline{ASTB}\downarrow$ to $\overline{WR}\downarrow$	t <sub>DSTW</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T – 9			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T – 9			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T – 20			ns
Data setup time (to $\overline{WR}\uparrow$ )	t <sub>SODWR</sub>	V <sub>DD</sub> = 5.0 V ±10%	(1.5 + n)T – 20			ns
		V <sub>DD</sub> = 3.0 V ±10%	(1.5 + n)T – 25			ns
		V <sub>DD</sub> = 2.0 V ±5%	(1.5 + n)T – 70			ns
Data hold time (from $\overline{WR}\uparrow$ )	t <sub>HWOD</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T – 14			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T – 14			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T – 50			ns
Delay time from $\overline{WR}\uparrow$ to $\overline{ASTB}\uparrow$	t <sub>DWST</sub>	V <sub>DD</sub> = 5.0 V ±10%	0.5T – 9			ns
		V <sub>DD</sub> = 3.0 V ±10%	0.5T – 9			ns
		V <sub>DD</sub> = 2.0 V ±5%	0.5T – 30			ns
$\overline{WR}$ low-level width	t <sub>WWL</sub>	V <sub>DD</sub> = 5.0 V ±10%	(1.5 + n)T – 25			ns
		V <sub>DD</sub> = 3.0 V ±10%	(1.5 + n)T – 30			ns
		V <sub>DD</sub> = 2.0 V ±5%	(1.5 + n)T – 30			ns

**Remark** T: t<sub>CYK</sub> = 1/f<sub>xx</sub> (f<sub>xx</sub>: main system clock frequency)

a: 1 (during address wait), otherwise, 0

n: Number of wait states (n ≥ 0)

AC Characteristics

(2) External wait timing

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input time from address to $\overline{\text{WAIT}}\downarrow$	$t_{\text{DAWT}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$			$(2 + a)T - 40$	ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$			$(2 + a)T - 60$	ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$			$(2 + a)T - 300$	ns
Input time from $\text{ASTB}\downarrow$ to $\overline{\text{WAIT}}\downarrow$	$t_{\text{DSTWT}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$			$1.5T - 40$	ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$			$1.5T - 60$	ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$			$1.5T - 260$	ns
Hold time from $\text{ASTB}\downarrow$ to $\overline{\text{WAIT}}$	$t_{\text{HSTWT}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$	$(0.5 + n)T + 5$			ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$	$(0.5 + n)T + 10$			ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$	$(0.5 + n)T + 30$			ns
Delay time from $\text{ASTB}\downarrow$ to $\overline{\text{WAIT}}\uparrow$	$t_{\text{DSTWTH}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$			$(1.5 + n)T - 40$	ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$			$(1.5 + n)T - 60$	ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$			$(1.5 + n)T - 90$	ns
Input time from $\overline{\text{RD}}\downarrow$ to $\overline{\text{WAIT}}\downarrow$	$t_{\text{DRWTL}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$			$T - 40$	ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$			$T - 60$	ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$			$T - 70$	ns
Hold time from $\overline{\text{RD}}\downarrow$ to $\overline{\text{WAIT}}\downarrow$	$t_{\text{HRWT}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$	$nT + 5$			ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$	$nT + 10$			ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$	$nT + 30$			ns
Delay time from $\overline{\text{RD}}\downarrow$ to $\overline{\text{WAIT}}\uparrow$	$t_{\text{DRWTH}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$			$(1 + n)T - 40$	ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$			$(1 + n)T - 60$	ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$			$(1 + n)T - 90$	ns
Data input time from $\overline{\text{WAIT}}\uparrow$	$t_{\text{DWTID}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$			$0.5T - 5$	ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$			$0.5T - 10$	ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$			$0.5T - 30$	ns
Delay time from $\overline{\text{WAIT}}\uparrow$ to $\overline{\text{RD}}\uparrow$	$t_{\text{DWTR}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$	$0.5T$			ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$	$0.5T$			ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$	$0.5T + 5$			ns
Delay time from $\overline{\text{WAIT}}\uparrow$ to $\overline{\text{WR}}\uparrow$	$t_{\text{DWTW}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$	$0.5T$			ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$	$0.5T$			ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$	$0.5T + 5$			ns
Input time from $\overline{\text{WR}}\downarrow$ to $\overline{\text{WAIT}}\downarrow$	$t_{\text{DWWTL}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$			$T - 40$	ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$			$T - 60$	ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$			$T - 90$	ns
Hold time from $\overline{\text{WR}}\downarrow$ to $\overline{\text{WAIT}}$	$t_{\text{HWWT}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$	$nT + 5$			ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$	$nT + 10$			ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$	$nT + 30$			ns
Delay time from $\overline{\text{WR}}\downarrow$ to $\overline{\text{WAIT}}\uparrow$	$t_{\text{DWWTH}}$	$V_{\text{DD}} = 5.0 \text{ V} \pm 10\%$			$(1 + n)T - 40$	ns
		$V_{\text{DD}} = 3.0 \text{ V} \pm 10\%$			$(1 + n)T - 60$	ns
		$V_{\text{DD}} = 2.0 \text{ V} \pm 5\%$			$(1 + n)T - 90$	ns

**Remark** T:  $t_{\text{CYK}} = 1/f_{\text{XX}}$  ( $f_{\text{XX}}$ : main system clock frequency)

a: 1 (during address wait), otherwise, 0

n: Number of wait states ( $n \geq 0$ )

**Serial Operation (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V)**

**(a) 3-wire serial I/O mode ( $\overline{\text{SCK}}$ : Internal clock output)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
$\overline{\text{SCK}}$ cycle time	t <sub>KCY1</sub>	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	800			ns
			3,200			ns
$\overline{\text{SCK}}$ high-/low-level width	t <sub>KH1</sub> , t <sub>KL1</sub>	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	350			ns
			1,500			ns
SI setup time (to $\overline{\text{SCK}}\uparrow$ )	t <sub>SIK1</sub>	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	10			ns
			30			ns
SI hold time (from $\overline{\text{SCK}}\uparrow$ )	t <sub>KSI1</sub>		40			ns
SO output delay time (from $\overline{\text{SCK}}\downarrow$ )	t <sub>KSO1</sub>				30	ns

**(b) 3-wire serial I/O mode ( $\overline{\text{SCK}}$ : External clock input)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
$\overline{\text{SCK}}$ cycle time	t <sub>KCY2</sub>	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	800			ns
			3,200			ns
$\overline{\text{SCK}}$ high-/low-level width	t <sub>KH2</sub> , t <sub>KL2</sub>	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	400			ns
			1,600			ns
SI setup time (to $\overline{\text{SCK}}\uparrow$ )	t <sub>SIK2</sub>	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	10			ns
			30			ns
SI hold time (from $\overline{\text{SCK}}\uparrow$ )	t <sub>KSI2</sub>		40			ns
SO output delay time (from $\overline{\text{SCK}}\downarrow$ )	t <sub>KSO2</sub>				30	ns

**(c) UART mode**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
ASCK cycle time	t <sub>KCY3</sub>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	417			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V	833			ns
			1,667			ns
ASCK high-/low-level width	t <sub>KH3</sub> , t <sub>KL3</sub>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	208			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V	416			ns
			833			ns

(d) I<sup>2</sup>C bus mode

Parameter	Symbol	Standard Mode		High-Speed Mode		Unit
		MIN.	MAX.	MIN.	MAX.	
SCL0 clock frequency	f <sub>CLK</sub>	0	100	0	400	kHz
Bus free time (between stop and start conditions)	t <sub>BUF</sub>	4.7	–	1.3	–	μs
Hold time <sup>Note 1</sup>	t <sub>HD : STA</sub>	4.0	–	0.6	–	μs
Low-level width of SCL0 clock	t <sub>LOW</sub>	4.7	–	1.3	–	μs
High-level width of SCL0 clock	t <sub>HIGH</sub>	4.0	–	0.6	–	μs
Setup time of start/restart conditions	t <sub>SU : STA</sub>	4.7	–	0.6	–	μs
Data hold time	When using CBUS-compatible master	t <sub>HD : DAT</sub>	5.0	–	–	μs
	When using I <sup>2</sup> C bus	t <sub>HD : DAT</sub>	0 <sup>Note 2</sup>	–	0 <sup>Note 2</sup>	0.9 <sup>Note 3</sup>
Data setup time	t <sub>SU : DAT</sub>	250	–	100 <sup>Note 4</sup>	–	ns
Rise time of SDA0 and SCL0 signals	t <sub>R</sub>	–	1,000	20 + 0.1Cb <sup>Note 5</sup>	300	ns
Fall time of SDA0 and SCL0 signals	t <sub>F</sub>	–	300	20 + 0.1Cb <sup>Note 5</sup>	300	ns
Setup time of stop condition	t <sub>SU : STO</sub>	4.0	–	0.6	–	μs
Pulse width of spike restricted by input filter	t <sub>SP</sub>	–	–	0	50	ns
Load capacitance of each bus line	C <sub>b</sub>	–	400	–	400	pF

- Notes**
- For the start condition, the first clock pulse is generated after the hold time.
  - To fill the undefined area of the SCL0 falling edge, it is necessary for the device to provide an internal SDA0 signal (on V<sub>IHmin.</sub>) with at least 300 ns of hold time.
  - If the device does not extend the SCL0 signal low-level hold time (t<sub>LOW</sub>), only the maximum data hold time t<sub>HD : DAT</sub> needs to be satisfied.
  - The high-speed mode I<sup>2</sup>C bus can be used in a standard mode I<sup>2</sup>C bus system. In this case, the conditions described below must be satisfied.
    - If the device does not extend the SCL0 signal low-level hold time  
t<sub>SU : DAT</sub> ≥ 250 ns
    - If the device extends the SCL0 signal low-level hold time  
Be sure to transmit the data bit to the SDA0 line before the SCL0 line is released (t<sub>Rmax.</sub> + t<sub>SU : DAT</sub> = 1,000 + 250 = 1,250 ns by standard mode I<sup>2</sup>C bus specification)
  - C<sub>b</sub>: Total capacitance per bus line (unit: pF)

**Other Operations (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
NMI high-/low-level width	t <sub>WNIL</sub> t <sub>WNIH</sub>		10			μs
Interrupt input high-/low-level width	t <sub>WITL</sub> t <sub>WITH</sub>	INTP0 to INTP6	100			ns
RESET high-/low-level width	t <sub>WRSL</sub> t <sub>WRSH</sub>		10			μs

**Clock Output Operation (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PCL cycle time	t <sub>CYCL</sub>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V, nT	80		31,250	ns
PCL high-/low-level width	t <sub>CLL</sub> t <sub>CLH</sub>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V, 0.5T - 10	30		15,615	ns
PCL rise/fall time	t <sub>CLR</sub> t <sub>CLF</sub>	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V			5	ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V			10	ns
		1.9 V ≤ V <sub>DD</sub> < 2.7 V			20	ns

**Remark** T: t<sub>CYK</sub> = 1/f<sub>XX</sub> (f<sub>XX</sub>: Main system clock frequency)

n: Divided frequency ratio set by software in the CPU

- When using the main system clock: n = 1, 2, 4, 8, 16, 32, 64, 128
- When using the subsystem clock: n = 1

**A/D Converter Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution			8	8	8	bits
Overall error <sup>Notes 1, 2</sup>		2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V 2.2 V ≤ AV <sub>REF0</sub> ≤ V <sub>DD</sub>			±1.2	%FSR
		1.9 V ≤ V <sub>DD</sub> < 2.7 V 1.9 V ≤ AV <sub>REF0</sub> ≤ V <sub>DD</sub>			±1.6	%FSR
Conversion time	t <sub>CONV</sub>		14		144	μs
Sampling time	t <sub>SAMP</sub>		24/f <sub>XX</sub>			μs
Analog input voltage	V <sub>IAN</sub>		AV <sub>SS</sub>		AV <sub>REF0</sub>	V
Reference voltage	AV <sub>REF0</sub>		1.9		AV <sub>DD</sub>	V
Resistance between AV <sub>REF0</sub> and AV <sub>SS</sub>	R <sub>AVREF0</sub>	When not A/D converting		40		kΩ

- Notes**
1. Quantization error (±1/2 LSB) is not included.
  2. Overall error is indicated as a ratio to the full-scale value.

**Remark** f<sub>XX</sub> : Main system clock frequency

**D/A Converter Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V)**

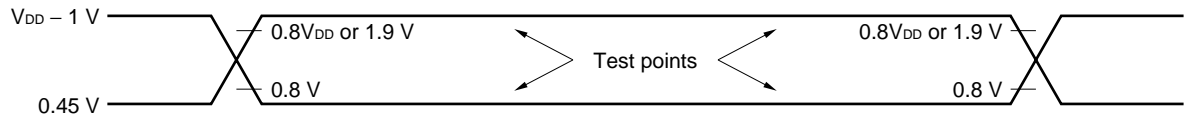
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Resolution			8	8	8	Bits	
Overall error <sup>Notes 1, 2</sup>		R = 10 MΩ, 2.0 V ≤ AV <sub>REF1</sub> ≤ V <sub>DD</sub> , 2.0 V ≤ V <sub>DD</sub> ≤ 5.5 V			±0.6	%FSR	
		R = 10 MΩ, 1.9 V ≤ AV <sub>REF1</sub> ≤ V <sub>DD</sub> , 1.9 V ≤ V <sub>DD</sub> ≤ 2.0 V			±1.2	%FSR	
Settling time		Load conditions: C = 30 pF	4.5 V ≤ AV <sub>REF1</sub> ≤ 5.5 V			10	μs
			2.7 V ≤ AV <sub>REF1</sub> < 4.5 V			15	μs
			1.9 V ≤ AV <sub>REF1</sub> < 2.7 V			20	μs
Output resistance	R <sub>O</sub>	DACS0, 1 = 55H		8		kΩ	
Reference voltage	AV <sub>REF1</sub>		1.9		V <sub>DD</sub>	V	
AV <sub>REF1</sub> current	AI <sub>REF1</sub>	For only 1 channel			2.5	mA	

- Notes**
1. Quantization error (±1/2 LSB) is not included.
  2. Overall error is indicated as a ratio to the full-scale value.

Data Retention Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = AV<sub>DD</sub> = 1.9 to 5.5 V, V<sub>SS</sub> = AV<sub>SS</sub> = 0 V)

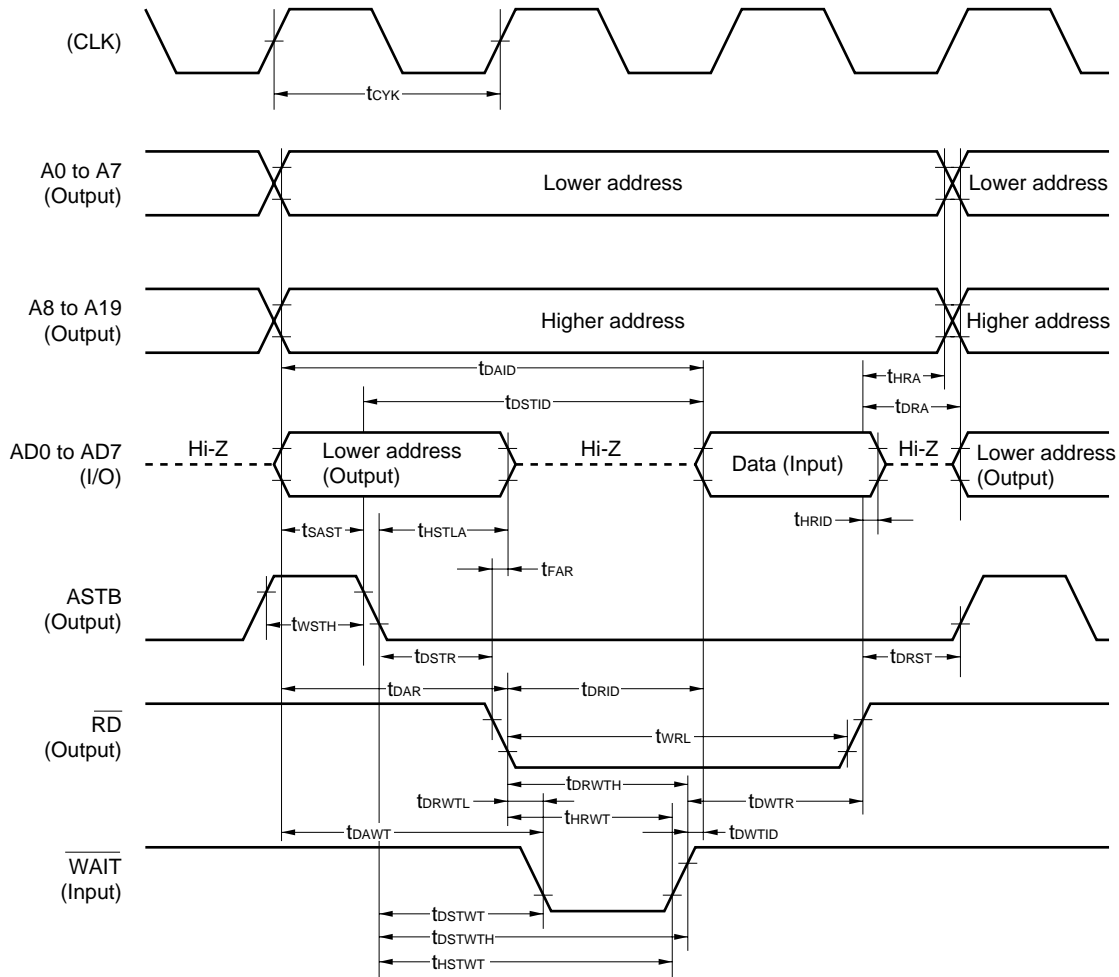
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention voltage	V <sub>DDDR</sub>	STOP mode	1.9		5.5	V
Data retention current	I <sub>DDDR</sub>	V <sub>DDDR</sub> = 5.0 V ±10%		10	50	μA
		V <sub>DDDR</sub> = 2.0 V ±5%		2	10	μA
V <sub>DD</sub> rise time	t <sub>RVD</sub>		200			μs
V <sub>DD</sub> fall time	t <sub>FVD</sub>		200			μs
V <sub>DD</sub> hold time (from STOP mode setting)	t <sub>HVD</sub>		0			ms
STOP release signal input time	t <sub>DREL</sub>		0			ms
Oscillation stabilization wait time	t <sub>WAIT</sub>	Crystal resonator	30			ms
		Ceramic resonator	5			ms
Low-level input voltage	V <sub>IL</sub>	RESET, P00/INTP0 to P06/INTP6	0		0.1V <sub>DDDR</sub>	V
High-level input voltage	V <sub>IH</sub>		0.9V <sub>DDDR</sub>		V <sub>DDDR</sub>	V

AC Timing Test Points



Timing Waveforms

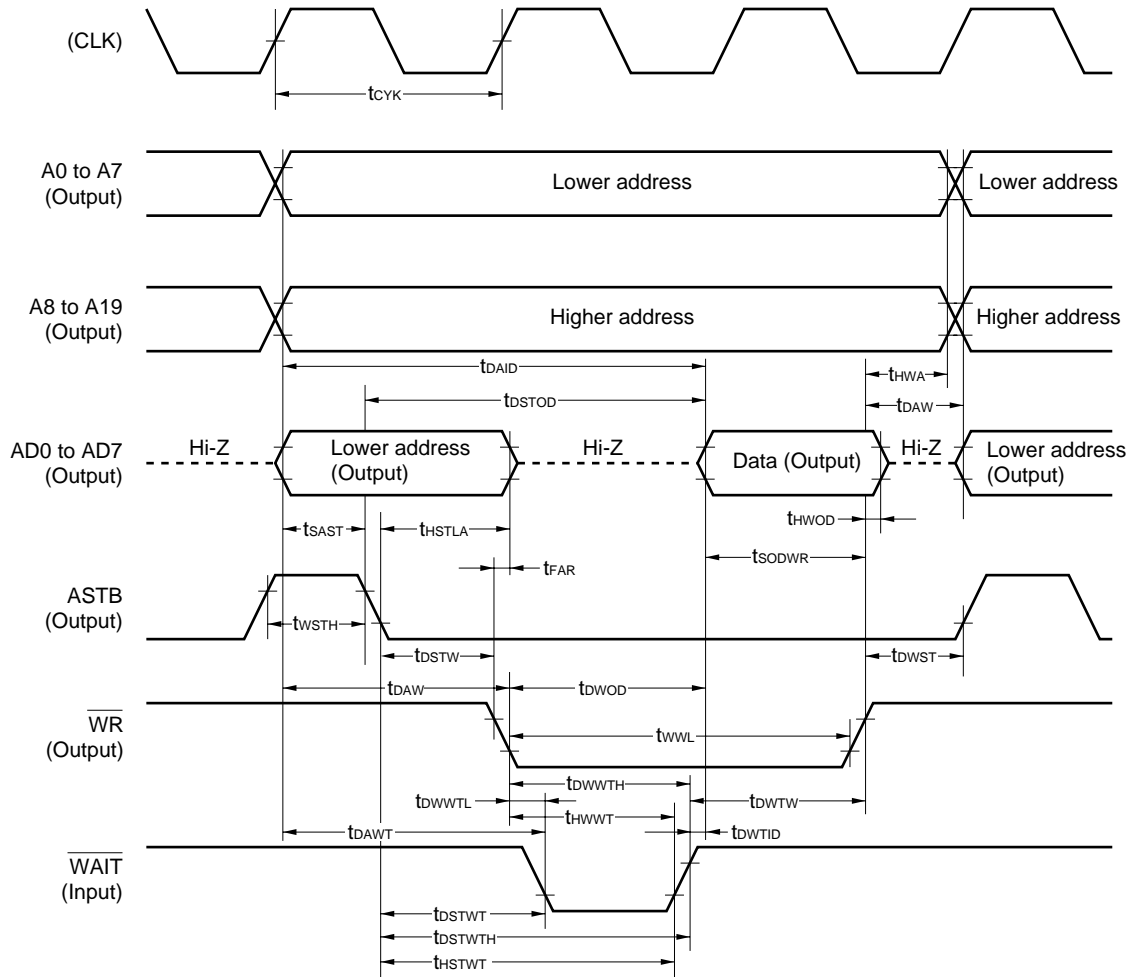
(1) Read operations



**Remark** The signal is output from pins A0 to A7 when P80 to P87 are unused.



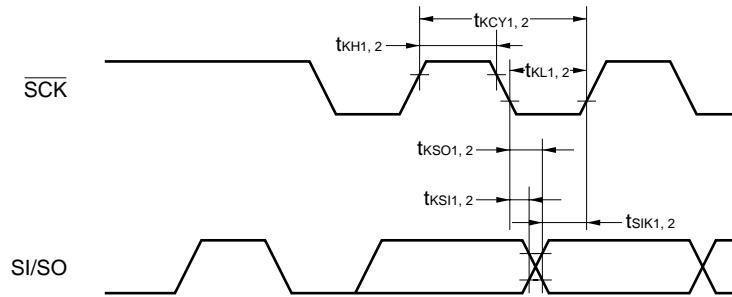
(2) Write operation



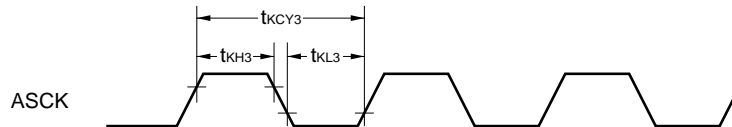
**Remark** The signal is output from pins A0 to A7 when P80 to P87 are unused.

Serial Operation

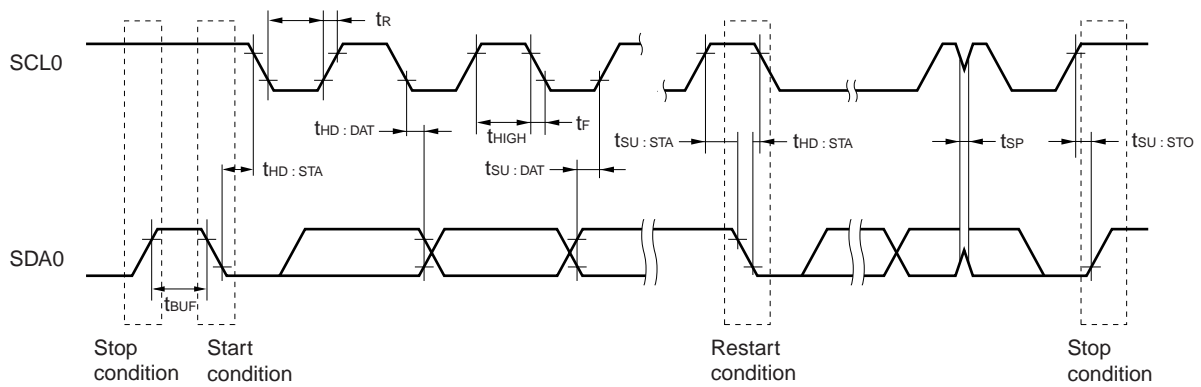
(1) 3-wire serial I/O mode



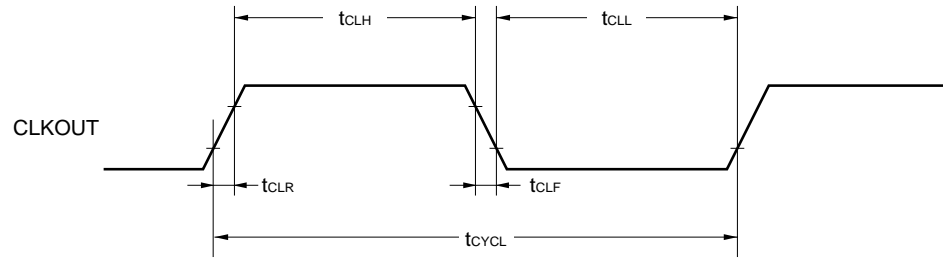
(2) UART mode



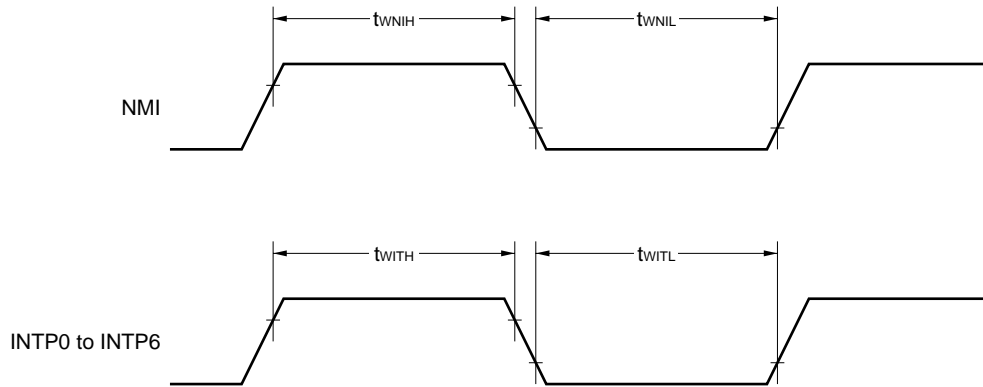
(3) I<sup>2</sup>C bus mode ( $\mu$ PD78F4216AY, 78F4218AY only)



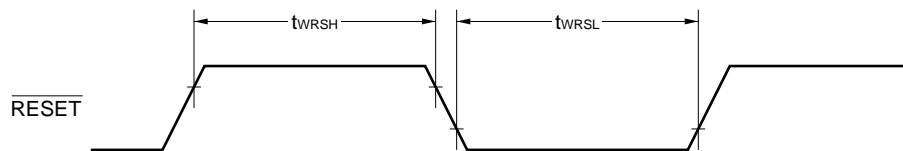
**Clock Output Timing**



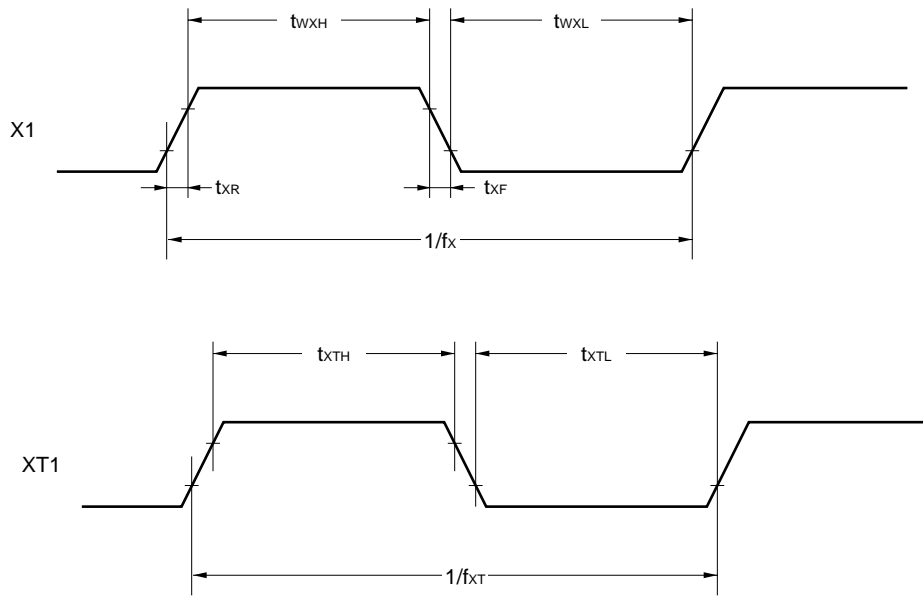
**Interrupt Input Timing**



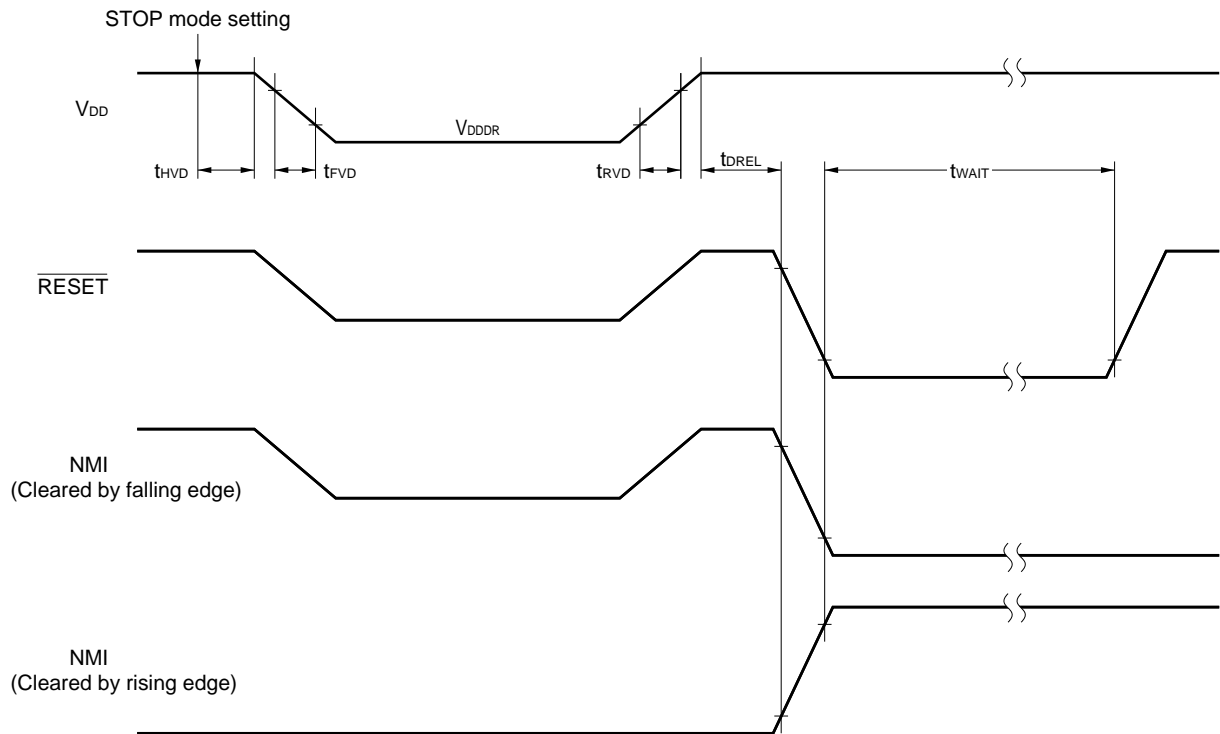
**Reset Input Timing**



**Clock Timing**



**Data Retention Characteristics**



**Flash Memory Programming Characteristics ( $V_{DD} = AV_{DD} = 1.9$  to  $5.5$  V,  $V_{SS} = AV_{SS} = 0$  V,  $V_{PP} = 9.7$  to  $10.3$  V)**

**(1) Basic characteristics**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Operating frequency	f <sub>x</sub>	$4.5\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2		12.5	MHz
		$2.7\text{ V} \leq V_{DD} < 4.5\text{ V}$	2		6.25	MHz
		$2.0\text{ V} \leq V_{DD} < 2.7\text{ V}$	2		3.125	MHz
		$1.9\text{ V} \leq V_{DD} < 2.0\text{ V}$	2	2	2	MHz
Supply voltage <sup>Note 1</sup>	V <sub>DD</sub>		1.9		5.5	V
	V <sub>PPL</sub>	Upon V <sub>PP</sub> low-level detection	0		0.2V <sub>DD</sub>	V
	V <sub>PP</sub>	Upon V <sub>PP</sub> high-level detection	0.9V <sub>DD</sub>	V <sub>DD</sub>	1.1V <sub>DD</sub>	V
	V <sub>PPH</sub>	Upon V <sub>PP</sub> high-voltage detection	9.7	10	10.3	V
V <sub>DD</sub> supply current	I <sub>DD</sub>			40	mA	
V <sub>PP</sub> supply current	I <sub>PP</sub>	V <sub>PP</sub> = 10 V			100	mA
Write count	C <sub>WRT</sub>		20 <sup>Note 2</sup>			Times
Operating temperature <sup>Note 3</sup>	T <sub>A</sub>		-40		85	°C
Storage temperature <sup>Note 4</sup>	T <sub>stg</sub>		-65		125	°C
Programming temperature	T <sub>PRG</sub>		10		40	°C

**Notes** 1. μPD78F4216A, 78F4216AY K standard:  $2.7\text{ V} \leq V_{DD} < 5.5\text{ V}$ ,  $V_{PP} = 10.3 \pm 0.3\text{ V}$   
 E standard:  $2.7\text{ V} \leq V_{DD} < 5.5\text{ V}$ ,  $V_{PP} = 10.0 \pm 0.3\text{ V}$

2. Operation cannot be guaranteed when the number of writes exceeds 20 times. In the case of the μPD78F4216A and 78F4216AY with K standard, operation cannot be guaranteed when the number of writes exceeds 5 times.
3. μPD78F4216A, 78F4216AY K standard: T<sub>A</sub> = -10 to +60°C
4. μPD78F4216A, 78F4216AY K standard: T<sub>A</sub> = -10 to +80°C

- Cautions** 1. If writing is not successful in write operation, execute the program command again, and execute the verify command to confirm the normal completion of the write operation.  
 (μPD78F4216A, 78F4216AY: I, K, E, P standard)
2. Handshake mode is supported by the following products.  
 μPD78F4216A, 78F4216AY: Other than I, K, E standard  
 μPD78F4218A, 78F4218AY: Other than I standard

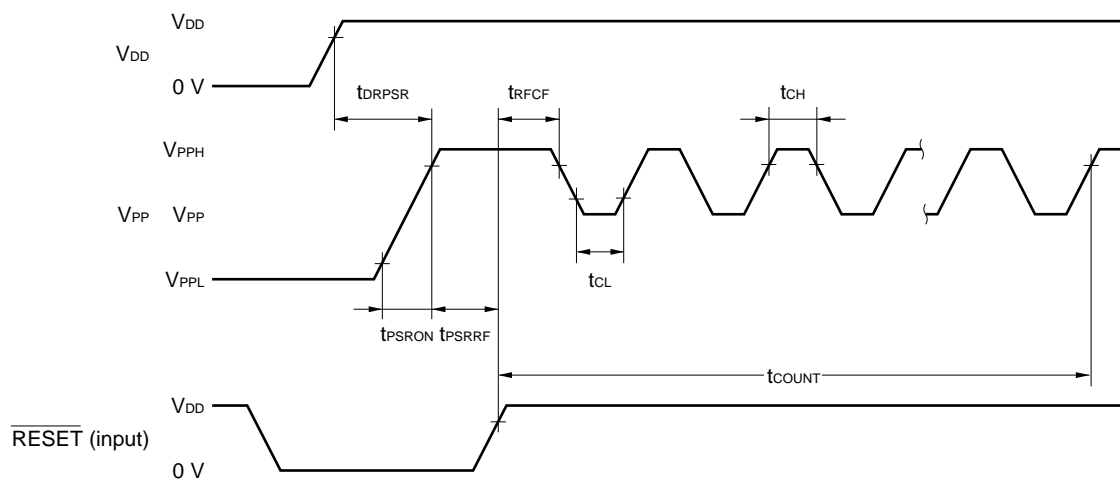
**Remark** The fifth alphabetic character from the left in the lot number indicates the standard of the product. After executing the program command, execute the verify command to confirm the normal completion of the write operation.  
 Handshake mode is the CSI write mode that uses P24.

**Flash Memory Programming Characteristics ( $V_{DD} = AV_{DD} = 1.9$  to  $5.5$  V,  $V_{SS} = AV_{SS} = 0$  V,  $V_{PP} = 9.7$  to  $10.3$  V)**

**(2) Serial write operation characteristics**

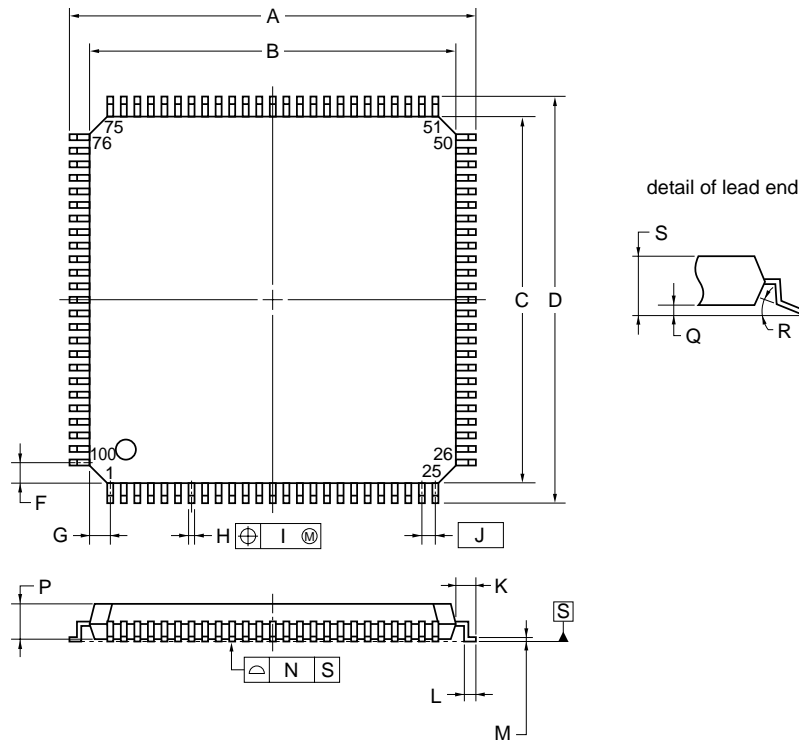
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
$V_{PP}$ setup time	$t_{PSRON}$	$V_{PP}$ high voltage	1.0			$\mu$ s
$V_{PP}\uparrow$ setup time to $V_{DD}\uparrow$	$t_{DRPSR}$	$V_{PP}$ high voltage	10			$\mu$ s
$\overline{RESET}\uparrow$ set up time to $V_{PP}\uparrow$	$t_{PSRRF}$	$V_{PP}$ high voltage	1.0			$\mu$ s
$V_{PP}$ count start time from $\overline{RESET}\uparrow$	$t_{RFCF}$		1.0			$\mu$ s
Count execution time	$t_{COUNT}$				1.0	ms
$V_{PP}$ counter high-level width	$t_{CH}$		8.0			$\mu$ s
$V_{PP}$ counter low-level width	$t_{CL}$		8.0			$\mu$ s
$V_{PP}$ counter noise elimination width	$t_{NFW}$			40		ns

**Flash Memory Write Mode Setting Timing**



8. PACKAGE DRAWINGS

100-PIN PLASTIC LQFP (FINE PITCH) (14x14)



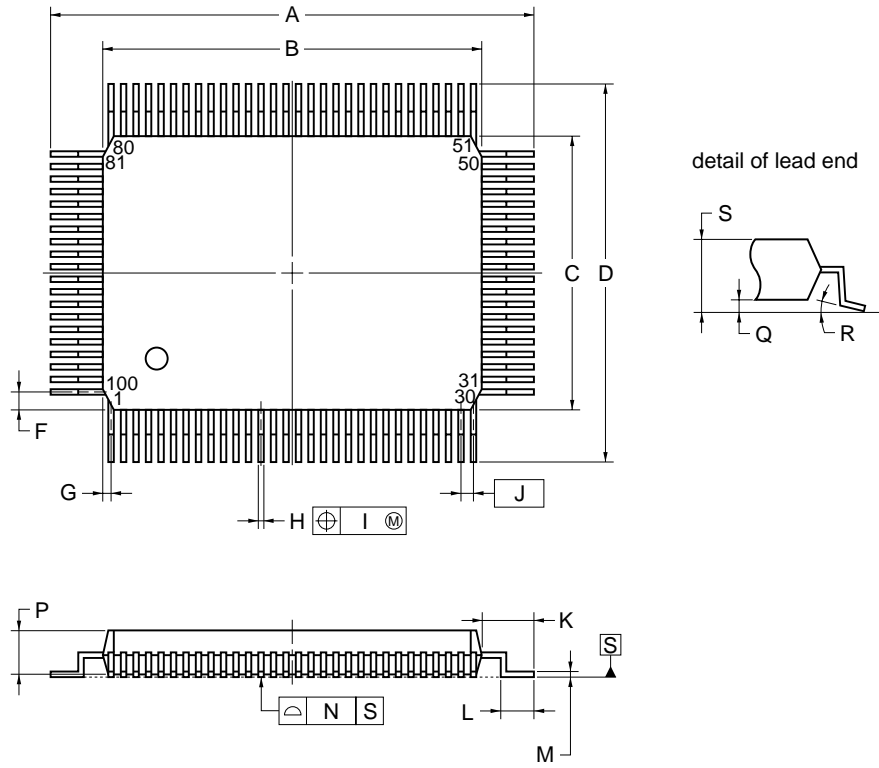
**NOTE**  
Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	16.00±0.20
B	14.00±0.20
C	14.00±0.20
D	16.00±0.20
F	1.00
G	1.00
H	0.22 <sup>+0.05</sup> <sub>-0.04</sub>
I	0.08
J	0.50 (T.P.)
K	1.00±0.20
L	0.50±0.20
M	0.17 <sup>+0.03</sup> <sub>-0.07</sub>
N	0.08
P	1.40±0.05
Q	0.10±0.05
R	3 <sup>+7°</sup> <sub>-3°</sub>
S	1.60 MAX.

S100GC-50-8EU, 8EA-2

**Remark** The external dimensions and material of the ES version are the same as those of the mass-produced version.

100-PIN PLASTIC QFP (14x20)



NOTE

Each lead centerline is located within 0.15 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	23.6±0.4
B	20.0±0.2
C	14.0±0.2
D	17.6±0.4
F	0.8
G	0.6
H	0.30±0.10
I	0.15
J	0.65 (T.P.)
K	1.8±0.2
L	0.8±0.2
M	0.15 <sup>+0.10</sup> <sub>-0.05</sub>
N	0.10
P	2.7±0.1
Q	0.1±0.1
R	5°±5°
S	3.0 MAX.

P100GF-65-3BA1-4

**Remark** The external dimensions and material of the ES version are the same as those of the mass-produced version.



**9. RECOMMENDED SOLDERING CONDITIONS**

The μPD78F4218AY should be soldered and mounted under the following recommended conditions. For the details of the recommended soldering conditions, refer to the document **Semiconductor Device Mounting Technology Manual (C10535E)**.

For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

**Table 9-1. Surface Mounting Type Soldering Conditions**

- (1) μPD78F4216AGC-8EU:100-pin plastic LQFP (fine pitch) (14 × 14)
- μPD78F4218AGC-8EU:100-pin plastic LQFP (fine pitch) (14 × 14)
- μPD78F4216AYGC-8EU:100-pin plastic LQFP (fine pitch) (14 × 14)
- μPD78F4218AYGC-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Two times or less, Exposure limit: 7 days <sup>Note</sup> (after that, prebake at 125°C for 10 hours)	IR35-107-2
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher), Count: Two times or less, Exposure limit: 7 days <sup>Note</sup> (after that, prebake at 125°C for 10 hours)	VP15-107-2
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	—

**Note** After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

**Caution** Do not use different soldering methods together (except for partial heating).

- (2) μPD78F4216AGF-3BA:100-pin plastic QFP (14 × 20)
- μPD78F4218AGF-3BA:100-pin plastic QFP (14 × 20)
- μPD78F4216AYGF-3BA:100-pin plastic QFP (14 × 20)
- μPD78F4218AYGF-3BA: 100-pin plastic QFP (14 × 20)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Two times or less	IR35-00-2
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher), Count: Two times or less	VP15-00-2
Wave soldering	Solder bath temperature: 260°C max., Time: 10 seconds max., Count: Once, Preheating temperature: 120°C max. (package surface temperature)	WS60-00-1
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	—

**Caution** Do not use different soldering methods together (except for partial heating).

## APPENDIX A. DEVELOPMENT TOOLS

The following development tools are available for system development using the  $\mu$ PD78F4218AY. Also refer to (5) Cautions on using development tools.

### (1) Language processing software

RA78K4	Assembler package common to 78K/IV Series
CC78K4	C compiler package common to 78K/IV Series
DF784218	Device file common to $\mu$ PD784216A, 784216AY, 784218A, 784218AY Subseries
CC78K4-L	C compiler library source file common to 78K/IV Series

### (2) Flash memory writing tools

Flashpro II (Part number: FL-PR2), Flashpro III (Part number: FL-PR3, PG-FP3)	Dedicated flash programmer for microcontroller incorporating flash memory
FA-100GF	Adapter for writing 100-pin plastic QFP (GF-3BA type) flash memory. Connection must be performed in accordance with the target product.
FA-100GC	Adapter for writing 100-pin plastic LQFP (GC-8EU type) flash memory. Connection must be performed in accordance with the target product.

### (3) Debugging tools

- When IE-78K4-NS in-circuit emulator is used

IE-78K4-NS	In-circuit emulator common to 78K/IV Series
IE-70000-MC-PS-B	Power supply unit for IE-78K4-NS
IE-70000-98-IF-C	Interface adapter required when PC-9800 series PC (except notebook type) is used as host machine (C bus supported)
IE-70000-CD-IF-A	PC card and cable when PC-9800 series notebook PC is used as host machine (PCMCIA socket supported)
IE-70000-PC-IF-C	Interface adapter required when using IBM PC/AT™ compatibles as host machine (ISA bus supported)
IE-70000-PCI-IF	Interface adapter required when using PC that incorporates PCI bus as host machine
IE-784225-NS-EM1	Emulation board to emulate $\mu$ PD784216A, 784216AY, 784218A, 784218AY Subseries
NP-100GF	Emulation probe for 100-pin plastic QFP (GF-3BA type)
NP-100GC	Emulation probe for 100-pin plastic LQFP (GC-8EU type)
EV-9200GF-100	Socket to be mounted on a target system board made for 100-pin plastic QFP (GF-3BA type)
TGC-100SDW	Conversion adapter to connect the NP-100GC and a target system board on which a 100-pin plastic LQFP (GC-8EU type) can be mounted
ID78K4-NS	Integrated debugger for IE-78K4-NS
SM78K4	System simulator common to 78K/IV Series
DF784218	Device file common to $\mu$ PD784216A, 784216AY, 784218A, 784218AY Subseries

• When IE-784000-R in-circuit emulator is used

IE-784000-R	In-circuit emulator common to 78K/IV Series
IE-70000-98-IF-C	Interface adapter required when PC-9800 series PC (except notebook type) is used as host machine (C bus supported)
IE-70000-PC-IF-C	Interface adapter required when using IBM PC/AT and compatibles as host machine (ISA bus supported)
IE-70000-PCI-IF	Interface adapter required when using PC that incorporates PCI bus as host machine
IE-78000-R-SV3	Interface adapter and cable required when EWS is used as host machine
IE-784225-NS-EM1	Emulation board to emulate μPD784216A, 784216AY, 784218A, 784218AY Subseries
IE-784000-R-EM	Emulation board common to 78K/IV Series
IE-78K4-R-EX3	Emulation probe conversion board required when using IE-784225-NS-EM1 on IE-784000-R.
EP-784218GF-R	Emulation probe for 100-pin plastic QFP (GF-3BA type)
EP-78064GC-R	Emulation probe for 100-pin plastic LQFP (GC-8EU type)
EV-9200GF-100	Socket to be mounted on a target system board made for 100-pin plastic QFP (GF-3BA type)
TGC-100SDW	Conversion adapter to connect the EP-78064GC-R and a target system board on which a 100-pin plastic LQFP (GC-8EU type) can be mounted
ID78K4	Integrated debugger for IE-784000-R
SM78K4	System simulator common to 78K/IV Series
DF784218	Device file common to μPD784216A, 784216AY, 784218A, 784218AY Subseries

(4) Real-time OS

RX78K/IV	Real-time OS for 78K/IV Series
MX78K4	OS for 78K/IV Series

**(5) Cautions on using development tools**

- The ID78K4-NS, ID78K4, and SM78K4 are used in combination with the DF784218.
- The CC78K4 and RX78K/IV are used in combination with the RA78K4 and DF784218.
- The FL-PR2, FL-PR3, FA-100GF, FA-100GC, NP-100GF, and NP-100GC are products made by Naito Densei Machida Mfg. Co., Ltd. (TEL: +81-44-822-3813).
- The TGC-100SDW is a product made by TOKYO ELETECH CORPORATION.

For further information, contact Daimaru Kogyo, Ltd.

Tokyo Electronic Division (TEL: +81-3-3820-7112)

Osaka Electronic Division (TEL: +81-6-6244-6672)

- For third party development tools, see the **Single-Chip Microcontroller Development Tool Selection Guide (U11069E)**.
- The host machine and OS suitable for each software are as follows:

Host Machine [OS] Software	PC	EWS
	PC-9800 series [Windows] IBM PC/AT and compatibles [Japanese/English Windows]	HP9000 Series 700™ [HP-UX™] SPARCstation™ [SunOS™, Solaris™] NEWS™ (RISC) [NEWS-OS™]
RA78K4	√ <b>Note</b>	√
CC78K4	√ <b>Note</b>	√
ID78K4-NS	√	–
ID78K4	√	√
SM78K4	√	–
RX78K/IV	√ <b>Note</b>	√
MX78K4	√ <b>Note</b>	√

**Note** DOS-based software

**APPENDIX B. RELATED DOCUMENTS**

**Documents related to devices**

Document Name	Document No.
μPD784214A, 784215A, 784216A, 784217A, 784218A, 784214AY, 784215AY, 784216AY, 784217AY, 784218AY Data Sheet	U14121E
μPD78F4216A, 78F4216AY, 78F4218A, 78F4218AY Data Sheet	This document
μPD784216A, 784216AY Subseries User's Manual Hardware	U13570E
μPD784218A, 784218AY Subseries User's Manual Hardware	U12970E
78K/IV Series User's Manual Instructions	U10905E
78K/IV Series Instruction Table	-
78K/IV Series Instruction Set	-
78K/IV Series Application Note Software Basics	-

**Documents related to development tools (user's manuals)**

Document Name	Document No.	
RA78K4 Assembler Package	Language	U11162E
	Operation	U11334E
RA78K Structured Assembler Preprocessor		U11743E
CC78K4 C Compiler	Language	U11571E
	Operation	U11572E
IE-78K4-NS		U13356E
IE-784000-R		U12903E
IE-784218-R-EM1		U12155E
IE-784225-NS-EM1		U13742E
EP-78064		EEU-1469
SM78K4 System Simulator Windows Based	Reference	U10093E
SM78K Series System Simulator	External Part User Open Interface Specifications	U10092E
ID78K4-NS Integrated Debugger PC Based	Reference	U12796E
ID78K4 Integrated Debugger Windows Based	Reference	U10440E
ID78K4 Integrated Debugger HP-UX, SunOS, NEWS-OS Based	Reference	U11960E

**Caution** The related documents listed above are subject to change without notice. Be sure to use the latest version of each document for designing.

**Documents related to embedded software (user's manuals)**

Document Name		Document No.
78K/IV Series Real-Time OS	Fundamental	U10603E
	Installation	U10604E
	Debugger	–
78K/IV Series OS MX78K4	Fundamental	–

**Other documents**

Document Name	Document No.
SEMICONDUCTOR SELECTION GUIDE Products & Packages (CD-ROM)	X13769X
Semiconductor Device Mounting Technology Manual	C10535E
Quality Grades on NEC Semiconductor Devices	C11531E
NEC Semiconductor Device Reliability/Quality Control System	C10983E
Guide to Prevent Damage for Semiconductor Devices by Electrostatic Discharge (ESD)	C11892E
Guide to Microcomputer-Related Products by Third Party	–

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[MEMO]

[MEMO]



[MEMO]

**NOTES FOR CMOS DEVICES****① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS**

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

**② HANDLING OF UNUSED INPUT PINS FOR CMOS**

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to  $V_{DD}$  or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

**③ STATUS BEFORE INITIALIZATION OF MOS DEVICES**

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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- Product release schedule
- Availability of related technical literature
- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
- Network requirements

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